Journal of Non-Crystalline Solids 114 (1989) 831–844
North-Holland

AUTHOR INDEX

Abeles, B., see Persans 114 (1989) 771
Abelson, J., Photoconductivity of hydrogenated amorphous silicon 114 (1989) 450
Abelson, J.R., see Maley 114 (1989) 163
Abelson, J.R., L. Mandrell, J.R. Doyle, A. Myers and N. Maley, Isotropic hydrogen exchange studies of the a-Si : H surface during growth 114 (1989) 184
Abkowitz, M. and M. Stolka, Transport in Si and Ge polymers above and below T_g – comparison with a-Se and other glasses 114 (1989) 342
Adriaenssens, G.J. and P. Nagels, Transient photocurrents in Bi-modified Ge_2Se_7 114 (1989) 100
Agrawal, B.K., P.S. Yadav and B.K. Ghosh, Vibrational excitations in a-$Si_{1-x}C_x$: H alloys 114 (1989) 519
Aiga, M., see Sasaki 114 (1989) 672
Aivazov, A.A., N.V. Bodyagin, S.P. Vikhrov and S.V. Petrov, Collective effects in the a-Si : H growth process 114 (1989) 157
Aiyah, V., see Kasap 114 (1989) 49
Al-Alawi, S., see Al-Dallal 114 (1989) 789
Al-Alawi, S.M., see Aljishi 114 (1989) 462
Al-Dallal, S., see Aljishi 114 (1989) 462
Al-Dallal, S., M. Hammam and S. Al-Alawi, Vibrational; electrical and optical properties of hydrogenated amorphous silicon–sulfur alloy 114 (1989) 789
Albright, D.E., see Saxena 114 (1989) 801
Aldea, A., The thermopower of non-localized electrons in amorphous semiconductors 114 (1989) 375
Aljishi, S., J.D. Cohen and L. Ley, Energy distribution and thermal broadening of band tail states in doped and undoped hydrogenated amorphous silicon 114 (1989) 247
Aljishi, S., M. Stutzmann, S. Jin, C. Herrero, S. Al-Dallal, M. Hammam and S.M. Al-Alawi, Defect density and structure of hydrogenated amorphous silicon–sulfur alloys 114 (1989) 462
Allain, B., see Driss Khodja 114 (1989) 498
Anderson, G.B., see Tsai 114 (1989) 151
Andriesh, A.M., I.P. Culiac and V.M. Loghin, Spectral intensity and time dependences of photoinduced optical absorption in glassy As_2S_3 114 (1989) 136
Antoniadis, H., see Hotaling 114 (1989) 420
Aoki, T., S. Kato, Y. Nishikawa and M. Hirose, Hydrogen dilution effects on properties of ECR plasma deposited a-Ge : H 114 (1989) 798
Arai, K., see Toyoshima 114 (1989) 819
Arai, T., Y. Wakayama, H. Kudo, T. Kishimoto, J. Lee, T. Ogawa and S. Onari, Ag photodoping in chalcogenide glass As_2S_3 114 (1989) 40
Arai, T., see Matsuishi 114 (1989) 46
Arasaki, A.T., see Carreño 114 (1989) 762
Arce, R., L. Ley and M. Hundhausen, Random telegraphic noise in large area a-Si : H/a-$Si_{1-x}N_x$: H double barrier structures 114 (1989) 696
Ardelean, I., see Chahed 114 (1989) 471
Arkhipov, V.I., C.R Nikitenko and A.I. Rudenko, Field-stimulated carrier diffusion in amorphous semiconductors 114 (1989) 366
Asal, R., see Davis 114 (1989) 465
Asano, A., T. Ichimura and H. Sakai, Preparation of highly photoconductive hydrogenated amorphous silicon carbide films with a multiplasma-zone apparatus 114 (1989) 175
Asano, A. and H. Sakai, Improvement in the boron-doping efficiency of hydrogenated amorphous silicon carbide films using BF_3 114 (1989) 268
Asomoza, R., see Reyes-Mena 114 (1989) 310
Azuma, H., see Hanna 114 (1989) 804
Azuma, M., see Hanna 114 (1989) 804

Baker, D.W., see Galloni 114 (1989) 271
Banerjee, R., see Okushi 114 (1989) 669
Baranovskii, S.D., see Shklovskii 114 (1989) 325
Barclay, R.P., M. Nesladek, T. Dyer and D. Kurnia, Investigation of the gap state distribution in a-Si : H using post-transit pulse analysis 114 (1989) 259
Barrio, R.A., see Chambouleyron 114 (1989) 558
Barua, A.K., see Das 114 (1989) 552
Barua, A.K., see Ganguly 114 (1989) 822
Bassler, H., see Silver 114 (1989) 244
Batabyal, A.K., see Das 114 (1989) 552
Bauer, G.H., see Lotter 114 (1989) 322
Bauer, G.H., see Eicke 114 (1989) 474
Bauer, G.H., see Schubert 114 (1989) 528
Bauer, G.H., see Nebel 114 (1989) 600
Bauer, G.H., see Schumm 114 (1989) 660
Baumvol, I.J.R., see Chambouleyron 114 (1989) 558
Bayliss, S.C., see Davis 114 (1989) 465
Bayliss, S.C., see Singh 114 (1989) 504

0022-3093/89/$03.50 © Elsevier Science Publishers B.V. (North-Holland)

Beeby, J.L. and T.M. Hayes, A calculation of the density of electronic states for amorphous semiconductors 114 (1989) 253
Benfatto, M., see Filipponi 114 (1989) 229
Berkin, J., see Marshall 114 (1989) 339
Berner, H., G. Kragler, J. Meier, M. Simon, H. Curtins and E. Bucher, Oxide growth on a-Si : H and its influence on surface gap states 114 (1989) 678
Beyer, W., see Horbach 114 (1989) 187
Beyer, W., J. Herion and H. Wagner, Fermi energy dependence of surface desorption and diffusion of hydrogen in a-Si : H 114 (1989) 217
Beyer, W., see Siebke 114 (1989) 357
Beyer, W., see Camargo Jr 114 (1989) 807
Bhat, P.K., see Shen 114 (1989) 265
Bilger, G., see Eicke 114 (1989) 474
Bo, J., see Guang 114 (1989) 576
Bodart, J., P. Santos-Filho and R.E. Norberg, Microcrystallinity and silyl rotors in a-Si : D;H films 114 (1989) 825
Bodyagin, N.V., see Aivazov 114 (1989) 157
Böhm, H., see Karg 114 (1989) 477
Boolchand, P., see Zitkovsky 114 (1989) 70
Bort, M., R. Carius and W. Fuhs, Lifetime distribution of the photoluminescence of a-Si : H and a-$Si_{1-x}C_x$: H 114 (1989) 280
Bort, M., see Liedtke 114 (1989) 522
Boscherini, F., S. Mobilio, F. Evangalisti and A.M. Flank, EXAFS determination of the local bonding configuration of P in a-Si : H 114 (1989) 223
Boyce, J.B., S.E. Ready, M. Stutzmann and R.E. Norberg, NMR investigation of hydrogen in amorphous silicon and related materials 114 (1989) 211
Boyce, J.B., see Nemanich 114 (1989) 813
Brabec, C.J., Intermediate range order in computer modeled a-As_2S_3 114 (1989) 73
Branz, H., see Silver 114 (1989) 244
Branz, H.M. and M. Silver, Charged dangling bonds: key to electronic transport; recombination and metastability in hydrogenated amorphous silicon 114 (1989) 639
Browne, A., see Marshall 114 (1989) 339
Bube, R.H., see Redfield 114 (1989) 621
Buchanan, W.A., see Fortmann 114 (1989) 624
Bucher, E., see Berner 114 (1989) 678
Buda, F., G.L. Chiarotti, I. Štich, R. Car and M. Parrinello, Ab-initio molecular-dynamics of liquid and amorphous semiconductors 114 (1989) 7
Buehler, E.C., see Nemanich 114 (1989) 813
Bulycheva, E.Yu., see Domashevskaya 114 (1989) 495
Burr, J.N., see Morgan 114 (1989) 262
Bustarret, E., Urbach edges and angular distortions in a-Si : H and related alloys 114 (1989) 13
Bustarret, E., Bond angle distortions and hydrogenation at the Si/a-SiN : H interface 114 (1989) 753
Cai, Y., see Thorpe 114 (1989) 19
Camargo Jr, S.S. and W. Beyer, Improvement of a-SiC : H alloys by hydrogen dilution of starting gases 114 (1989) 807
Campbell, I.H., see Fauchet 114 (1989) 277
Campbell, I.H., see Saxena 114 (1989) 801
Campbell, I.H., see Okada 114 (1989) 816
Car, R., see Buda 114 (1989) 7
Carius, R., see Bort 114 (1989) 280
Carius, R. and F. Finger, Influence of the defect concentration on the recombination in electron bombarded a-Si : Ge : H alloys studied by photoluminescence and electron spin resonance 114 (1989) 549
Carlsson, A.E., see Fedders 114 (1989) 393
Carreño, M.N.P., I. Pereyra, A. Komazawa and A.T. Arasaki, Negative resistance in a-SiC_x : H double barrier devices – frequency dependence 114 (1989) 762
Chahed, L., A. Gheorghiu, M.L. Theye, I. Ardelean, C. Senemaud and C. Godet, Studies of the density of states at the band edges and in the pseudo-gap in a-SiGe : H alloys by combined photothermal deflection spectroscopy and X-ray spectroscopy 114 (1989) 471
Chambouleyron, I., F.C. Marques, I.J.R. Baumvol and R.A. Barrio, The structure of defects in amorphous germanium tin-alloys 114 (1989) 558
Chambouleyron, I., see Marques 114 (1989) 561
Chao, S.S., see Reyes-Mena 114 (1989) 310
Chen, G., see Yu 114 (1989) 429
Chen, G., see He 114 (1989) 657
Chen, H., see Chen 114 (1989) 759
Chen, J., see Zhang 114 (1989) 510
Chen, J., see Okada 114 (1989) 816
Chen, K., G. Mao, Z. Li, H. Chen, Z. Ge and H. Fritzsche, Nature of AX center in amorphous silicon/nitride multilayers 114 (1989) 759
Chen, K., G. Mao, S. Jiang, H. Xia, D. Feng and H. Fritzsche, New results in quasi-periodic amorphous semiconductor superlattices 114 (1989) 780
Chen, L., J. Tauc, J.-K. Lee and E.A. Schiff, Photomodulation spectroscopy of defects in hydrogenated amorphous silicon germanium alloys 114 (1989) 585
Chen, W., see He 114 (1989) 657
Cheng, R., see Zhang 114 (1989) 510
Cheng, R., see Wang 114 (1989) 702
Cheng, R., see Wang 114 (1989) 741
Chernyshov, S.V., see Vassilyev 114 (1989) 507
Chiarotti, G.L., see Buda 114 (1989) 7

Chik, K.P., see Du 114 (1989) 369
Chik, K.P., see Ong 114 (1989) 783
Cho, G., see Quereshi 114 (1989) 417
Choi, W.K., see Hajto 114 (1989) 304
Chu, V., see Wagner 114 (1989) 453
Chu, V., see Conde 114 (1989) 693
Cohen, J.D., see Aljishi 114 (1989) 247
Cohen, J.D., Capacitance studies of deep defects in hydrogenated amorphous silicon 114 (1989) 381
Cohen, J.D., see Essick 114 (1989) 435
Cohen, J.D., see Unold 114 (1989) 603
Collins, R.W., Dielectric functions of thin interface layers in a-Si : H-based device structures by spectroscopic ellipsometry 114 (1989) 160
Conde, J.P., see Wagner 114 (1989) 453
Conde, J.P., V. Chu and S. Wagner, Breaking the isotropy of amorphous silicon–germanium alloys: graded-bandgap and sawtooth superlattice structures 114 (1989) 693
Corcotoi, I., see Grigorovici 114 (1989) 256
Corey, R.L., see Santos-Filho 114 (1989) 235
Crandall, R.S., see Williamson 114 (1989) 226
Crandall, R.S., Defect relaxation in hydrogenated amorphous silicon 114 (1989) 597
Crandall, R.S., see McMahon 114 (1989) 615
Crowder, M.S., see Kanicki 114 (1989) 612
Culiac, I.P., see Andriesh 114 (1989) 136
Cuniot, M., see Lequeux 114 (1989) 555
Curtins, H., see Kočka 114 (1989) 336
Curtins, H., see Favre 114 (1989) 405
Curtins, H., see Berner 114 (1989) 678

Das, D., S.C. De, S. Ray, A.K. Batabyal and A.K. Barua, Device quality a-SiGe : H films for multijunction solar cells 114 (1989) 552
Dauwen, J. and W. Grevendonk, Temperature dependence of photo-induced absorption in several a-Si : H samples with different hydrogen content 114 (1989) 295
Davidson, B.N., see Lucovsky 114 (1989) 154
Davidson, B.N., see Esser 114 (1989) 573
Davidson, B.N., G. Lucovsky, G.N. Parsons, R.J. Nemanich, A. Esser, K. Seibert and H. Kurz, Free carrier absorption and the transient optical properties of amorphous silicon thin films: a model including time dependent free carrier; and static and dispersive interband contributions to the complex dielectric constant 114 (1989) 579
Davis, E.A., S.C. Bayliss, R. Asal and M. Manssor, Free-carrier behaviour in a-$Si_{1-y}Ni_y$: H 114 (1989) 465
Davis, E.A., see Singh 114 (1989) 504
De, S.C., see Das 114 (1989) 552
De, S.C., see Ganguly 114 (1989) 822
De Angelis, L., see Grillo 114 (1989) 750
De Rosny, G., see Hadjeris 114 (1989) 301
De Rosny, G., see Labdi 114 (1989) 399
Deguchi, M., see Sasaki 114 (1989) 672
Deimel, P.P., see Wind 114 (1989) 531
Dejus, R.J., D.J. Le Poire, D.L. Price, S. Susman and K.J. Volin, Effect of alloying with silver on intermediate-range order in bulk germanium diselenide glasses 114 (1989) 37
Delahoy, A., see Liu 114 (1989) 363
Dembovsky, S.A., Model of chalcogenide glassy semiconductors based on three-center bonds in a rigid covalent network 114 (1989) 115
Demichelis, F. and A. Tagliaferro, Annealing temperature dependence of conductivity in a-CSiGe : H alloys deposited at different substrate temperatures 114 (1989) 468
Deng, X.-M., H. Fritzsche and R. Johanson, Study of artificial interfaces in undoped and phosphorus doped a-Si : H 114 (1989) 684
Deseta, M., see Fiorini 114 (1989) 732
Desyatirikova, E.N., see Domashevskaya 114 (1989) 495
Devlen, R.I., J.A. Moon, J. Tauc and Z. Vardeny, Picosecond studies of saturation of electron trapping on P_4^+ states in a-Si : H : P 114 (1989) 289
Devlen, R.I., J. Tauc and E.A. Schiff, Temperature and electric field dependence of the picosecond electron drift velocity in a-Si : H 114 (1989) 567
Di Cicco, A., see Filipponi 114 (1989) 229
Djebbour, Z., see Kleider 114 (1989) 432
Djebbour, Z., see Godet 114 (1989) 534
Dodds, D., see Kasap 114 (1989) 106
Domashevskaya, E.P., Yu.K. Timoshenko, V.A. Terekhov, E.N. Desyatirikova, E.Yu. Bulycheva and V.N. Seleznev, Electronic structure of a-Si_3N_4: ab initio cluster calculations and soft X-ray emission spectroscopy study 114 (1989) 495
Doyle, J.R., see Abelson 114 (1989) 184
Drevillon, B., In situ studies of the growth of hydrogenated amorphous silicon 114 (1989) 139
Driss Khodja, M., A. Le Corre, C. Senemaud, A. Gheorghiu, M.L. Theye, B. Allain and J. Perrin, Alloying effects on the electronic structure of a-$Si_{1-x}N_x$: H films prepared by a mercury-photosensitized decomposition method 114 (1989) 498
Du, N., Y.T. Zhu, B.Y. Tong, P.K. John, S.K. Wong and K.P. Chik, Normal Hall coefficient of LPCVD amorphous silicon 114 (1989) 369
Dürrwächter, M., see Ott 114 (1989) 828
Dyer, T., see Barclay 114 (1989) 259

Eberhardt, K., see Schubert 114 (1989) 528
Eicke, A., G. Bilger and G.H. Bauer, Chemical and structural analysis of a-SiGe : H by SIMS and XPS investigations 114 (1989) 474

Elliott, S.R., see Verrall 114 (1989) 34
Endo, T., see Wei 114 (1989) 735
Enomoto, T., see Hattori 114 (1989) 711
Equer, B., see Hadjeris 114 (1989) 301
Equer, B., see Labdi 114 (1989) 399
Esser, A., K. Seibert, H. Kurz, G.N. Parsons, C. Wang, B.N. Davidson, G. Lucovsky and R.J. Nemanich, Ultrafast recombination and trapping in amorphous silicon 114 (1989) 573
Esser, A., see Davidson 114 (1989) 579
Essick, J.M. and J.D. Cohen, The nature of the midgap defect transition in intrinsic a-Si:H as deduced by depletion width modulation electron spin resonance 114 (1989) 435
Evangalisti, F., see Boscherini 114 (1989) 223
Evangelisti, F., see Marques 114 (1989) 561
Evangelisti, F., see Fiorini 114 (1989) 732
Ewen, P.J.S., see Zakery 114 (1989) 109

Fauchet, P.M., I.H. Campbell, S.A. Lyon and R.J. Nemanich, Luminescence above the Tauc gap in a-Si:H 114 (1989) 277
Fauchet, P.M., A. Mourchid, D. Hulin, C. Tanguy and R. Vanderhaghen, Extended state mobility in a-Si:H measured by femtosecond spectroscopy 114 (1989) 564
Fauchet, P.M., see Mourchid 114 (1989) 582
Fauchet, P.M., see Saxena 114 (1989) 801
Fauchet, P.M., see Okada 114 (1989) 816
Favre, M., H. Curtins and M. Vanecek, Light scattering effects in CPM and PDS measurement on a-Si:H films 114 (1989) 405
Fedders, P.A., see Santos-Filho 114 (1989) 235
Fedders, P.A. and A.E. Carlsson, Environmental effects on dangling and floating bonds in amorphous Si 114 (1989) 393
Fedders, P.A., see Volz 114 (1989) 546
Feng, D., see Chen 114 (1989) 780
Feng, X., see Liu 114 (1989) 738
Ferreira, I., see Martins 114 (1989) 486
Filipponi, A., A. Di Cicco, M. Benfatto and C.R. Natoli, X-ray absorption spectroscopy on amorphous silicon: a probe for the three-body correlation function 114 (1989) 229
Finger, F., see Fuhs 114 (1989) 387
Finger, F., see Schütte 114 (1989) 411
Finger, F., see Carius 114 (1989) 549
Finger, F., see Schneider 114 (1989) 633
Fiorini, P., M. Deseta and F. Evangelisti, Photoconductivity and interface defects in a-SiH/a-$Si_{1-x}C_x$:H multi-quantum-well structures 114 (1989) 732
Fischer, R. and E.O. Gobel, Carrier relaxation in a-$Si_{1-x}C_x$:H studied by picoseond photoluminescence spectroscopy 114 (1989) 570
Flank, A.M., see Boscherini 114 (1989) 223
Fontaine, A., see Lee 114 (1989) 52
Fortmann, C.M., T.X. Zhou and W.A. Buchanan, The relationship between hydrogen content; weak bond density and Staebler–Wronski defects in amorphous silicon 114 (1989) 624
Fortmann, C.M., see Saxena 114 (1989) 801
Fortner, J., see Shao 114 (1989) 232
Fortner, J., R.Q. Yu and J.S. Lannin, Raman scattering and surface disorder in amorphous germanium 114 (1989) 675
Fortunato, E., see Martins 114 (1989) 486
Fortunato, G., L. Mariucci, C. Reita and V. Parisi, Experimental and theoretical evidence of space-charge photomodulation in metal/insulator/amorphous semiconductor structures 114 (1989) 378
French, I.D., see Powell 114 (1989) 642
Fritzsche, H., Low temperature electronic transport in non-crystalline semiconductors 114 (1989) 1
Fritzsche, H., see Johanson 114 (1989) 274
Fritzsche, H., see Shklovskii 114 (1989) 325
Fritzsche, H., see Deng 114 (1989) 684
Fritzsche, H., see Hamed 114 (1989) 717
Fritzsche, H., see Wang 114 (1989) 741
Fritzsche, H., see Chen 114 (1989) 759
Fritzsche, H., see Chen 114 (1989) 780
Fuhs, W., see Sotiropoulos 114 (1989) 97
Fuhs, W., see Bort 114 (1989) 280
Fuhs, W., see Jahn 114 (1989) 307
Fuhs, W. and F. Finger, Defects and recombination in a-$Si_{1-x}Ge_x$:H 114 (1989) 387
Fuhs, W., see Schütte 114 (1989) 411
Fuhs, W., see Liedtke 114 (1989) 522
Fuhs, W., see Pierz 114 (1989) 651
Fujieda, I., see Quereshi 114 (1989) 417
Fujii, T., see Onuki 114 (1989) 792
Fujita, Y., see Yamaguchi 114 (1989) 283
Furui, T., see Okushi 114 (1989) 669

Galloni, R., Y.S. Tsuo, D.W. Baker and F. Zignani, Boron doping and hydrogenation by ion implantation of a-Si:H 114 (1989) 271
Ganguly, G., S.C. De, S. Ray and A.K. Barua, PECVD of microcrystalline silicon carbon alloy thin films 114 (1989) 822
Gartner, P., see Grigorovici 114 (1989) 256
Ge, Z., see Chen 114 (1989) 759
Geissberger, A.E., see Zallen 114 (1989) 795
Gelatos, A., see Kanicki 114 (1989) 612
Gelatos, A., P. Wagner and J. Kanicki, Investigation of the plasma deposited silicon dioxide on hydrogenated amorphous silicon interface by capacitance measurements 114 (1989) 699
Georgieva, I., see Vateva 114 (1989) 124
Gerstein, B.C., see Shao 114 (1989) 232

Gheorghiu, A., see Chahed 114 (1989) 471
Gheorghiu, A., see Driss Khodja 114 (1989) 498
Ghosh, B.K., see Agrawal 114 (1989) 519
Gobel, E.O., see Fischer 114 (1989) 570
Godet, C., see Meaudre 114 (1989) 360
Godet, C., see Chahed 114 (1989) 471
Godet, C., A. Labdi, J.-P. Kleider, D. Mencaraglia and Z. Djebbour, Evolution of the density of states profile above mid-gap in a-SiGe : H alloys from complementary transport measurements 114 (1989) 534
Gonzalez-Hernandez, J., see Reyes-Mena 114 (1989) 310
Grevendonk, W., see Dauwen 114 (1989) 295
Grigorovici, R., P. Gartner and I. Corcotoi, Valence band density of states in amorphous silicon deduced from SPD orbitals 114 (1989) 256
Grillo, G. and L. De Angelis, Surface states and in-depth inhomogeneity in a-Si : H thin films: effects on the shape of the PDS sub-gap spectra 114 (1989) 750
Guang, H.X., W.H. Zhou, Y.Z. Xin, J. Bo and P. Shaoqi, Picosecond photoluminescence of a-Si : H/a-SiN_x : H multilayers with different nitrogen content 114 (1989) 576
Guimarães, L., see Martins 114 (1989) 486

Hadjeris, L., G. De Rosny and B. Equer, Electrostriction; electroabsorption and electroreflectance in a-Si : H 114 (1989) 301
Hafner, J., see Jank 114 (1989) 16
Haghani, M.A., see Ott 114 (1989) 828
Hajto, J., I. Janossy, W.K. Choi and A.E. Owen, Model of laser induced regular and chaotic oscillations in amorphous $GeSe_2$ films 114 (1989) 304
Haku, H., see Nishikuni 114 (1989) 181
Halpern, V., Non-radiative recombination at dangling bonds in a-Si : H 114 (1989) 441
Hamakawa, Y., see Tsutsumi 114 (1989) 627
Hamakawa, Y., see Hattori 114 (1989) 687
Hamakawa, Y., see Wei 114 (1989) 735
Hamed, A. and H. Fritzsche, The origin of persistent photoconductance in doping-modulated and compensated a-Si : H 114 (1989) 717
Hammam, M., see Aljishi 114 (1989) 462
Hammam, M., see Al-Dallal 114 (1989) 789
Han, D., see Xiao 114 (1989) 438
Han, D., see Wu 114 (1989) 606
Han, S., B. Hess, X. Wei, Z. Vardeny and S. Nitta, Picosecond and CW photomodulation spectroscopy of polysilane alloys 114 (1989) 588
Hanna, J., A. Kamo, T. Komiya, I. Shimizu and H. Kokado, Preparation of Si thin films by spontaneous chemical deposition 114 (1989) 172
Hanna, J., H. Azuma, H. Shirai, M. Azuma and I. Shimizu, Atomic hydrogen improves the rigidity of Si-network and tail states at the valence band in a-Si : H and a-Si : H(F) films 114 (1989) 804
Hanna, J., see Shirai 114 (1989) 810
Hartrott, M.v., see Ott 114 (1989) 828
Hattori, K., H. Okamoto and Y. Hamakawa, Optical approach to subband structure in a-Si quantum well 114 (1989) 687
Hattori, R., T. Enomoto and J. Shirafuji, Time-of-flight measurement of longitudinal electron transport in amorphous semiconductor multilayers 114 (1989) 711
Hattori, S., see Nonomura 114 (1989) 729
Hautala, J., S. Yamasaki and P.C. Taylor, Dependence of effective electron–electron correlation energies of defects on average coordination number in chalcogenide glasses 114 (1989) 85
Hautala, J., see Ristein 114 (1989) 444
Hayashi, H., see Nonomura 114 (1989) 729
Hayes, T.M., see Beeby 114 (1989) 253
Hazama, Y., see Miyazaki 114 (1989) 774
Hazama, Y., K. Yamada, S. Miyazaki and M. Hirose, a-Si_3N_4 : H/a-Si : H superlattices produced by plasma enhanced nitridation of a-Si : H 114 (1989) 777
He, D., F. Zhang, W. Chen and G. Chen, In situ electron spin resonance measurements of thermally induced metastable defects in doped hydrogenated amorphous silicon carbon films 114 (1989) 657
He, Z.G., see Jung 114 (1989) 55
Herion, J., see Beyer 114 (1989) 217
Herion, J., see Siebke 114 (1989) 357
Herrero, C., see Aljishi 114 (1989) 462
Hess, B., see Han 114 (1989) 588
Hickey, B.J., see Morgan 114 (1989) 262
Hirai, T., see Tsuji 114 (1989) 94
Hirose, M., see Miyazaki 114 (1989) 774
Hirose, M., see Hazama 114 (1989) 777
Hirose, M., see Aoki 114 (1989) 798
Holtz, M., see Zallen 114 (1989) 795
Honma, I., H. Komiyama and K. Tanaka, Growth process and structural disorder of reactively-sputtered a-Si : H/a-SiN_x multilayer films 114 (1989) 726
Horbach, C., W. Beyer and H. Wagner, Deposition of a-Si : H by high temperature thermal decomposition of silane 114 (1989) 187
Hotaling, S.P., H. Antoniadis and E.A. Schiff, Electron mobility-lifetime product and D° defect density in hydrogenated amorphous silicon 114 (1989) 420
Hotham, C., see Marshall 114 (1989) 339
Hubin, J., see Shah 114 (1989) 402
Hughes, J.R., see Powell 114 (1989) 642
Hulin, D., see Fauchet 114 (1989) 564

Hulin, D., see Mourchid 114 (1989) 582
Hundhausen, M., see Arce 114 (1989) 696
Hundhausen, M., Thermally stimulated conductivity in a-Si : H doping superlattices 114 (1989) 720

Ichimura, T., see Asano 114 (1989) 175
Imagawa, O., see Shimakawa 114 (1989) 345
Imamura, S., Y. Kanemitsu, M. Saito and H. Sugimoto, Carrier transport in amorphous chalcogenide multilayer structures 114 (1989) 121
Isomira, M., see Nishikuni 114 (1989) 181
Itoh, T., S. Nitta and S. Nonomura, Optical properties of amorphous multilayers a-Si : H/a-Si_3N_4 : H with random well or barrier layer thickness 114 (1989) 723
Itoh, T., see Nonomura 114 (1989) 729
Iwai, T., see Naito 114 (1989) 112

Jackson, W., C.C. Tsai and R. Thompson, Estimates of the diffusion rate of the dominant paramagnetic defect in hydrogenated amorphous silicon 114 (1989) 396
Jackson, W., Kinetics of metastable states in hydrogenated amorphous silicon 114 (1989) 591
Jackson, W.A., see Searle 114 (1989) 286
Jahn, K., W. Fuhs and K. Pierz, Field-dependent recombination in a-Si : H 114 (1989) 307
Jahn, K., see Liedtke 114 (1989) 522
Jang, J., see Song 114 (1989) 666
Jank, W. and J. Hafner, Electronic structure of molten Si; Ge and GaAs 114 (1989) 16
Janossy, I., see Hajto 114 (1989) 304
Jensen, P., see Meaudre 114 (1989) 360
Jiang, S., see Chen 114 (1989) 780
Jin, S., see Aljishi 114 (1989) 462
Johanson, R., see Deng 114 (1989) 684
Johanson, R.E., H. Fritzsche and A. Vomvas, Universal behavior of the normalized photoconductivity at low temperatures in amorphous semiconductors 114 (1989) 274
John, P.K., see Du 114 (1989) 369
Johnson, N.M., R.A. Street, J. Walker and K. Winer, Solid-source doping of a-Si : H thin films deposited with a remote hydrogen plasma 114 (1989) 169
Jones, S.J., W.A. Turner and W. Paul, The effect of sample substrate on the structural properties of co-deposited a-Ge : H films 114 (1989) 525
Jousse, D., see Kanicki 114 (1989) 612
Jukonis, G., see Juška 114 (1989) 354
Jung, A.-L., H. Situ, Y.W. Lu, Z.T. Wang and Z.G. He, Fast transformation mechanism of chalcogenide alloy glasses 114 (1989) 55
Juška, F., see Kočka 114 (1989) 336
Juška, G., G. Jukonis and J. Koč ka, Study of a-Si : H drift mobility in subnanosecond time scale 114 (1989) 354

Kakalios, J., A physical interpretation of the Hall effect in amorphous semiconductors 114 (1989) 372
Kakalios, J., The origin of persistent photoconductivity in amorphous silicon 114 (1989) 714
Kalbitzer, S., see Searle 114 (1989) 286
Kameyama, T., see Shimakawa 114 (1989) 786
Kamo, A., see Hanna 114 (1989) 172
Kanemitsu, Y., see Imamura 114 (1989) 121
Kanicki, J., D. Jousse, A. Gelatos and M.S. Crowder, Light-induced effects in hydrogenated amorphous nitrogen-rich silicon nitride films 114 (1989) 612
Kanicki, J., see Gelatos 114 (1989) 699
Kaplan, S.N., see Quereshi 114 (1989) 417
Karg, F.H., H. Böhm and K. Pierz, Influence of plasma deposition on structural and electronic properties of a-Ge : H 114 (1989) 477
Kasamura, J., see Matsuishi 114 (1989) 46
Kasap, S.O., B. Polischuk, V. Aiyah and S. Yannacopoulos, Thermal; mechanical and electrical relaxation phenomena in a-Se films 114 (1989) 49
Kasap, S.O., B. Polischuk, D. Dodds and S. Yannacopoulos, Charge trapping studies in a-Se films via interrupted field TOF technique 114 (1989) 106
Katiyar, M., see Maley 114 (1989) 163
Kato, S., see Aoki 114 (1989) 798
Kawamura, T., see Nakayama 114 (1989) 747
Kawasaki, M., M. Nakano, Y. Matsuzaki and H. Koinuma, Structural characterization of amorphous semiconductor heterojunctions by in situ XPS 114 (1989) 756
Kazanskii, A.G. and I.V. Klimashin, The influence of temperature on recombination of carriers in undoped a-Si : H 114 (1989) 313
Kidoh, H., see Shimizu 114 (1989) 630
Kim, M.-S., see Yoon 114 (1989) 636
Kim, Y.W., see Santos-Filho 114 (1989) 235
Kishimoto, T., see Arai 114 (1989) 40
Kleider, J.P., D. Mencaraglia and Z. Djebbour, A new treatment of Schottky barrier capacitance–voltage characteristics: discussion of usual assumptions and determination of the deep gap states density in a-$Si_{1-x}Ge_x$: H alloys 114 (1989) 432
Kleider, J.-P., see Godet 114 (1989) 534
Klimashin, I.V., see Kazanskii 114 (1989) 313
Koč ka, J., see Juška 114 (1989) 354
Kočka, J., E. Šípek, O. Štika, H. Curtins and F. Juška, a-Si : H drift mobility – study of isotropy 114 (1989) 336
Kočka, J., see Vaněček 114 (1989) 447
Kohda, Y., see Miyazaki 114 (1989) 774
Koinuma, H., see Kawasaki 114 (1989) 756
Kokado, H., see Hanna 114 (1989) 172
Komazawa, A., see Carreño 114 (1989) 762

Komiya, T., see Hanna 114 (1989) 172
Komiyama, H., see Honma 114 (1989) 726
Kondo, M. and K. Morigaki, Optically detected electron nuclear double resonance in a-Si : H 114 (1989) 408
Kondo, M., see Yokomichi 114 (1989) 426
Konkov, O.I., see Kudoyarova 114 (1989) 205
Kounavis, P. and E. Mytilineou, Drift mobility and photoconductivity for p- and n-type sputtered $Ge_{25}Se_{75-x}Bi_x$ films 114 (1989) 103
Kragler, G., see Berner 114 (1989) 678
Kramer, B. and M. Schreiber, Mesoscopic effects in the conductivity of amorphous semiconductors 114 (1989) 330
Krötz, G., see Wind 114 (1989) 531
Krötz, G., J. Wind and G. Müller, Field-effect-induced metastable conductivity changes in n-type a-Si : H 114 (1989) 663
Kruangam, D., see Wei 114 (1989) 735
Kubota, H., see Onuki 114 (1989) 792
Kudo, H., see Arai 114 (1989) 40
Kudoyarova, V.Kh., O.I. Konkov, E.I. Terukov, A.P. Sokolov and A.P. Shebanin, Correlation of Raman spectra with optical and electronic properties of a-Si : H 114 (1989) 205
Kumar, S., see Lee 114 (1989) 316
Kumeda, M., S. Nakanishi and T. Shimizu, Comparative study of the incorporation scheme of H in a-Si : H alloyed with C; N and O 114 (1989) 516
Kumeda, M., see Shimizu 114 (1989) 630
Kumeda, M., see Shimizu 114 (1989) 648
Kunst, M., see Neitzert 114 (1989) 166
Kurnia, D., see Barclay 114 (1989) 259
Kurz, H., see Esser 114 (1989) 573
Kurz, H., see Davidson 114 (1989) 579
Kusakabe, H., see Shimizu 114 (1989) 196
Kuwano, Y., see Nishikuni 114 (1989) 181

Labdi, A., G. de Rosny and B. Equer, Conduction properties of thin $N^+/I/N^+$ a-Si : H structures 114 (1989) 399
Labdi, A., see Godet 114 (1989) 534
Lanford, W., see Persans 114 (1989) 771
Lannin, J.S., see Shao 114 (1989) 232
Lannin, J.S., see Li 114 (1989) 543
Lannin, J.S., see Fortner 114 (1989) 675
Le Corre, A., see Driss Khodja 114 (1989) 498
Le Poire, D.J., see Dejus 114 (1989) 37
Lee, C., see Yoon 114 (1989) 636
Lee, C., see Song 114 (1989) 666
Lee, J., see Arai 114 (1989) 40
Lee, J.-K. and E.A. Schiff, The electron spin resonance lineshape in hydrogenated amorphous silicon germanium alloys 114 (1989) 423
Lee, J.-K., see Chen 114 (1989) 585
Lee, J.M., see Zhou 114 (1989) 43
Lee, J.M., G. Pfeiffer, M.A. Paesler, D.E. Sayers and A. Fontaine , Photon intensity-dependent darkening kinetics in optical and structural anisotropy in a-As_2S_3: a study of X-ray absorption spectroscopy 114 (1989) 52
Lee, S., S. Kumar, C.R. Wronski and N. Maley, A critical investigation of a-Si : H photoconductivity generated by subgap absorption of light 114 (1989) 316
Legrice, Y.M., see Nemanich 114 (1989) 813
Leidner, M., see Martin 114 (1989) 537
Lequeux, N. and M. Cuniot, Internal photoemission measurements on a-$Si_{1-x}Ge_x$: H/c-Si heterojunctions 114 (1989) 555
Lewis, L.J., see Mousseau 114 (1989) 202
Ley, L., Electronic structure of a-Si : H and its interfaces as determined by photoelectron spectroscopy 114 (1989) 238
Ley, L., see Aljishi 114 (1989) 247
Ley, L., see Arce 114 (1989) 696
Li, F., see Shao 114 (1989) 232
Li, F. and J.S. Lannin, Raman scattering in a-$Ge_{1-x}Si_x$: H alloys 114 (1989) 543
Li, Z., see Chen 114 (1989) 759
Liedtke, S., K. Lips, M. Bort, K. Jahn and W. Fuhs, Photoluminescence and optically detected magnetic resonance of a-Si_{1-x}-C_x : H films 114 (1989) 522
Lips, K., see Liedtke 114 (1989) 522
Liu, H., Z. Zhao, X. Feng, Z. Wang and W. Tang, Investigation into influence of nitrogen content on the interface disorder and optical properties multilayers of a-SiH/a-SiN_x : H 114 (1989) 738
Liu, J.Z. and P.C. Taylor, The formal valence shell model for structure of amorphous semiconductors 114 (1989) 25
Liu, J.Z., see Roca i Cabarrocas 114 (1989) 190
Liu, J.Z., A. Maruyama, S. Wagner and A. Delahoy, The steady state hole mobility lifetime product in undoped a-Si : H 114 (1989) 363
Liu, J.Z., see Wagner 114 (1989) 453
Loghin, V.M., see Andriesh 114 (1989) 136
Long, A.R., The influence of long range potential fluctuations on frequency dependent transport in a-Si : H 114 (1989) 348
Longeaud, C., see Vanderhaghen 114 (1989) 540
Lotter, E. and G.H. Bauer, Temperature dependent optical absorption measurements on a-Si : H; a-Ge : H; and a-SiGe : H by PDS 114 (1989) 322
Lu, Y.W., see Jung 114 (1989) 55
Lucovsky, G., B.N. Davidson, G.N. Parsons and C. Wang, Incorporation of polyhydride bonding groups into thin films of hydrogenated amorphous silicon (a-Si : H) 114 (1989) 154

Lucovsky, G., see Parsons 114 (1989) 178
Lucovsky, G., see Wang 114 (1989) 193
Lucovsky, G., see Yin 114 (1989) 459
Lucovsky, G., see Tsu 114 (1989) 501
Lucovsky, G., see Esser 114 (1989) 573
Lucovsky, G., see Davidson 114 (1989) 579
Lucovsky, G., see Nemanich 114 (1989) 813
Lyon, S.A., see Fauchet 114 (1989) 277
Lyubin, V.M. and V.K. Tikhomirov, Photodarkening and photoinduced anisotropy in chalcogenide vitreous semiconductor films 114 (1989) 133

Maçarico, A., see Martins 114 (1989) 486
Mahan, A.H., see Williamson 114 (1989) 226
Main, C., see Marshall 114 (1989) 339
Maley, N., I. Szafranek, L. Mandrell, M. Katiyar, J.R. Abelson and J.A. Thorton, Infrared reflectance spectroscopy of very thin films of a-SiH 114 (1989) 163
Maley, N., see Abelson 114 (1989) 184
Maley, N., see Lee 114 (1989) 316
Malinovsky, V.K., V.N. Novikov and A.P. Sokolov, Structural difference of two classes of amorphous semiconductors 114 (1989) 61
Mandrell, L., see Maley 114 (1989) 163
Mandrell, L., see Abelson 114 (1989) 184
Manssor, M., see Davis 114 (1989) 465
Mao, G., see Chen 114 (1989) 759
Mao, G., see Chen 114 (1989) 780
Mariucci, L., see Fortunato 114 (1989) 378
Marques, F.C., see Chambouleyron 114 (1989) 558
Marques, F.C., I. Chambouleyron and F. Evangelisti, Infrared analysis of a-$Ge_{1-x}N_x$: H 114 (1989) 561
Marshall, J.M., C. Pickup, A. Browne, J. McNeil, C. Hotham, C. Main and J. Berkin, Band tail states in a-Si : H – influence of preparation conditions and techniques for characterisation 114 (1989) 339
Martin, D., B. Schroeder, M. Leidner and H. Oechsner, Correlation between the structural and the electronic transport properties of sputtered hydrogenated amorphous germanium films 114 (1989) 537
Martins, R., G. Willeke, E. Fortunato, I. Ferreira, M. Vieira, M. Santos, A. Maçarico and L. Guimarães, Transport in μc-$Si_x : C_y : O_z$: H films prepared by a TCDDC system 114 (1989) 486
Maruyama, A., see Roca i Cabarrocas 114 (1989) 190
Maruyama, A., see Liu 114 (1989) 363
Matsuda, A., see Smith 114 (1989) 480
Matsuda, A., see Toyoshima 114 (1989) 819
Matsuishi, K., J. Kasamura, S. Onari and T. Arai, Intermediate range correlation in a-$Se_{1-x}Te_x$ and a-$(As_2S_3)_{1-x}Ag_x$ systems 114 (1989) 46
Matsumoto, M., see Shimizu 114 (1989) 630
Matsuoka, T., see Nishikuni 114 (1989) 181
Matsushita, T., see Naito 114 (1989) 112
Matsuura, H., see Smith 114 (1989) 480
Matsuura, H., Optically and thermally induced reversible changes of midgap states in undoped a-Si : H 114 (1989) 609
Matsuzaki, Y., see Kawasaki 114 (1989) 756
McMahon, T.J. and R.S. Crandall, Safe hole trap conversion properties and microscopic models 114 (1989) 615
McNeil, J., see Marshall 114 (1989) 339
McNeil, L.E. and M.J. Peters, Intercluster and intracluster interactions in $Ge_{1-x}Sn_xSe_2$ 114 (1989) 64
McNeil, L.E., see Mikrut 114 (1989) 127
Meaudre, M., see Meaudre 114 (1989) 360
Meaudre, R., P. Jensen, M. Meaudre and C. Godet, The preexponential factor of the electrical conductivity of undoped amorphous silicon 114 (1989) 360
Meier, J., see Berner 114 (1989) 678
Mell, H., see Weiser 114 (1989) 298
Mell, H., see Wiech 114 (1989) 492
Mell, H., see Pierz 114 (1989) 651
Mencaraglia, D., see Kleider 114 (1989) 432
Mencaraglia, D., see Godet 114 (1989) 534
Mikrut, J.M. and L.E. McNeil, Photostructural changes in bulk amorphous $Ge_{1-x}Sn_xSe_2$ 114 (1989) 127
Mitra, S., see Shinar 114 (1989) 220
Mitra, S., see Shao 114 (1989) 232
Miyazaki, S., Y. Kohda, Y. Hazama and M. Hirose, Stuctural characterization of amorphous silicon multilayer interfaces 114 (1989) 774
Miyazaki, S., see Hazama 114 (1989) 777
Mobilio, S., see Boscherini 114 (1989) 223
Moon, J.A., see Devlen 114 (1989) 289
Morgan, G.J., B.J. Hickey and J.N. Burr, The nature of the band gap in amorphous semiconductors 114 (1989) 262
Morigaki, K., see Yamaguchi 114 (1989) 283
Morigaki, K., see Yoshida 114 (1989) 319
Morigaki, K., see Kondo 114 (1989) 408
Morigaki, K., see Yokomichi 114 (1989) 426
Morigaki, K., see Yamaguchi 114 (1989) 705
Morimoto, A., see Shimizu 114 (1989) 630
Morimoto, A., see Shimizu 114 (1989) 648
Mourchid, A., see Fauchet 114 (1989) 564
Mourchid, A., R. Vanderhaghen, D. Hulin, C. Tanguy and P.M. Fauchet, Femtosecond optical spectroscopy in a-Si : H and its alloys 114 (1989) 582
Mousseau, N. and L.J. Lewis,

Computer-simulated model structures for hydrogenated amorphous semiconductors 114 (1989) 202
Müller, G., see Wind 114 (1989) 531
Müller, G., see Krötz 114 (1989) 663
Musabekov, E., see Vassilyev 114 (1989) 507
Myers, A., see Abelson 114 (1989) 184
Mytilineou, E., see Kounavis 114 (1989) 103

Nagels, P., see Adriaenssens 114 (1989) 100
Naito, H., T. Iwai, M. Okuda, T. Matsushita and A. Sugimura, Computer simulation study of tail-state distribution in amorphous selenium 114 (1989) 112
Nakanishi, S., see Kumeda 114 (1989) 516
Nakano, M., see Kawasaki 114 (1989) 756
Nakano, S., see Nishikuni 114 (1989) 181
Nakao, S., see Shimizu 114 (1989) 196
Nakayama, Y., T. Takahashi, K. Watanabe and T. Kawamura, Structure of interfaces in a-Si:H/a-Si_3N_4:H multilayers produced by plasma CVD 114 (1989) 747
Natoli, C.R., see Filipponi 114 (1989) 229
Nebel, C.E. and G.H. Bauer, Deep valence-band trap defect conversion by light soaking of a-Si:H 114 (1989) 600
Neitzert, H.C., A. Werner and M. Kunst, Charge carrier kinetics during growth of a-Si:H layers 114 (1989) 166
Nelson, B.P., see Williamson 114 (1989) 226
Nemanich, R.J., see Fauchet 114 (1989) 277
Nemanich, R.J., see Esser 114 (1989) 573
Nemanich, R.J., see Davidson 114 (1989) 579
Nemanich, R.J., E.C. Buehler, Y.M. Legrice, R.E. Shroder, G.N. Parsons, C. Wang, G. Lucovsky and J.B. Boyce, Raman scattering from microcrystalline Si films: considerations of composite structures with different optical absorption properties 114 (1989) 813
Nesladek, M., see Barclay 114 (1989) 259
Ninomiya, T., see Tada 114 (1989) 88
Nishikawa, Y., see Aoki 114 (1989) 798
Nishikuni, M., H. Haku, M. Isomira, S. Okamoto, K. Sayama, T. Takahama, T. Matsuoka, S. Tsuda, S. Nakano, M. Ohnishi and Y. Kuwano, Controlling hydrogen contents and bond configurations for high-quality and high-reliability a-Si films 114 (1989) 181
Nitta, S., see Han 114 (1989) 588
Nitta, S., see Itoh 114 (1989) 723
Nitta, S., see Nonomura 114 (1989) 729
Noda, M., see Shimizu 114 (1989) 196
Nonomura, S., see Itoh 114 (1989) 723
Nonomura, S., S. Hattori, H. Hayashi, T. Itoh and S. Nitta, Electronic states and structures of quasi-one-dimensional a-Si:H 114 (1989) 729
Norberg, R.E., see Boyce 114 (1989) 211
Norberg, R.E., see Santos-Filho 114 (1989) 235
Norberg, R.E., see Volz 114 (1989) 546
Norberg, R.E., see Bodart 114 (1989) 825
Novikov, V.N., see Malinovsky 114 (1989) 61

Oechsner, H., see Sopka 114 (1989) 208
Oechsner, H., see Martin 114 (1989) 537
Ogawa, T., see Arai 114 (1989) 40
Ogihara, C., see Yamaguchi 114 (1989) 705
Oheda, H., see Smith 114 (1989) 480
Ohlsen, W.D., see Ristein 114 (1989) 91
Ohnishi, M., see Nishikuni 114 (1989) 181
Ohta, H., see Yamaguchi 114 (1989) 705
Okada, T., see Shimakawa 114 (1989) 345
Okada, Y., J. Chen, I.H. Campbell, P.M. Fauchet and S. Wagner, Mechanism of microcrystalline silicon growth from silicon tetrafluoride and hydrogen 114 (1989) 816
Okamoto, H., see Tsutsumi 114 (1989) 627
Okamoto, H., see Hattori 114 (1989) 687
Okamoto, H., see Wei 114 (1989) 735
Okamoto, S., see Nishikuni 114 (1989) 181
Okuda, M., see Naito 114 (1989) 112
Okushi, H., R. Banerjee, T. Furui and K. Tanaka, Thermally- and light-induced metastable states in p-doped a-Si:H 114 (1989) 669
Onari, S., see Arai 114 (1989) 40
Onari, S., see Matsuishi 114 (1989) 46
Ong, C.W., K.P. Chik and H.K. Wong, Properties of a-boron films prepared by low pressure chemical vapour deposition 114 (1989) 783
Onuki, M., T. Fujii and H. Kubota, Time-of-flight measurement of hydrogenated amorphous GaP 114 (1989) 792
Ott, K., M. Dürrwächter, M.A. Haghani, M. v. Hartrott, B. Sauer and D. Quitmann, Knight shifts and bonding in liquid semiconductors 114 (1989) 828
Owen, A.E., see Zakery 114 (1989) 109
Owen, A.E., see Hajto 114 (1989) 304

Paesler, M.A., see Zhou 114 (1989) 43
Paesler, M.A., see Lee 114 (1989) 52
Paesler, M.A., see Yang 114 (1989) 67
Paesler, M.A., see Pfeiffer 114 (1989) 130
Paesler, M.A., see Tsu 114 (1989) 199
Pankove, J.I., see Wu 114 (1989) 606
Pantojas, V., see Persans 114 (1989) 771
Parisi, V., see Fortunato 114 (1989) 378
Park, H.R., see Roca i Cabarrocas 114 (1989) 190
Parrinello, M., see Buda 114 (1989) 7
Parsons, G.N., see Lucovsky 114 (1989) 154
Parsons, G.N., C. Wang, M.J. Williams and G. Lucovsky, Reduction of defects by high temperature annealing (150°C–240°C) in hydrogenated amorphous silicon films deposited at room temperature 114 (1989) 178

Parsons, G.N., see Wang 114 (1989) 193
Parsons, G.N., see Esser 114 (1989) 573
Parsons, G.N., see Davidson 114 (1989) 579
Parsons, G.N., see Nemanich 114 (1989) 813
Paul, W., see Santos-Filho 114 (1989) 235
Paul, W., see Jones 114 (1989) 525
Paul, W., see Zallen 114 (1989) 795
Pautmeier, L., see Silver 114 (1989) 244
Penfold, I.T. and P.S. Salmon, The coordination environment of Ag in glassy $AgAsS_2$. A neutron diffraction study 114 (1989) 82
Pereyra, I., see Carreño 114 (1989) 762
Perez-Mendez, V., see Quereshi 114 (1989) 417
Perrin, J., see Driss Khodja 114 (1989) 498
Persans, P.D., A.F. Ruppert, Y.-J. Wu, B. Abeles, W. Lanford and V. Pantojas, Stability of tetrahedrally-bonded amorphous semiconductor multilayers 114 (1989) 771
Peters, M.J., see McNeil 114 (1989) 64
Petrov, S.V., see Aivazov 114 (1989) 157
Petrova-Koch, V., see Wind 114 (1989) 531
Pfeiffer, G., see Lee 114 (1989) 52
Pfeiffer, G. and M.A. Paesler, Identification of IRO structures in photodarkening: a high pressure study of As_2S_3 114 (1989) 130
Pickup, C., see Marshall 114 (1989) 339
Pierz, K., see Jahn 114 (1989) 307
Pierz, K., see Karg 114 (1989) 477
Pierz, K., W. Fuhs and H. Mell, Correlation between defect density and Fermi-level position in a-Si : H 114 (1989) 651
Pirogov, F.V., The role of the medium range order in photocrystallization of chalcogenide glasses 114 (1989) 76
Polischuk, B., see Kasap 114 (1989) 49
Polischuk, B., see Kasap 114 (1989) 106
Powell, M.J., I.D. French and J.R. Hughes, Evidence for the defect pool concept for Si dangling bond states in a-Si : H from experiments with thin film transistors 114 (1989) 642
Price, D.L., see Dejus 114 (1989) 37

Qi, M., see Zhang 114 (1989) 510
Quereshi, S., V. Perez-Mendez, S.N. Kaplan, I. Fujieda, G. Cho and R.A. Street, Material parameters in thick hydrogenated amorphous silicon radiation detectors 114 (1989) 417
Quitmann, D., see Ott 114 (1989) 828

R. Nikitenko, C., see Arkhipov 114 (1989) 366
Ray, S., see Das 114 (1989) 552
Ray, S., see Ganguly 114 (1989) 822
Ready, S.E., see Boyce 114 (1989) 211
Redfield, D. and R.H. Bube, Defect kinetics in a-Si : H – an alternative description 114 (1989) 621
Reita, C., see Fortunato 114 (1989) 378
Reyes-Mena, A., R. Asomoza, J. Gonzalez-Hernandez and S.S. Chao, Influence of the structure on the recombination process in a-C : H films 114 (1989) 310
Ristein, J., P.C. Taylor, W.D. Ohlsen and G. Weiser, Optically detected magnetic resonance of intrinsic luminescence in As_2Se_3 114 (1989) 91
Ristein, J., J. Hautala and P.C. Taylor, Defect spectroscopy in a-Si : H using infrared excited luminescence and electron spin resonance 114 (1989) 444
Roca i Cabarrocas, P., J.Z. Liu, H.R. Park, A. Maruyama and S. Wagner, Substrate temperature dependence of the growth kinetics and opto-electronic properties of a-Si : H films deposited by RF glow discharge 114 (1989) 190
Rudenko, A.I., see Arkhipov 114 (1989) 366
Ruppert, A.F., see Persans 114 (1989) 771
Russell, T.W.F., see Saxena 114 (1989) 801

Sadler, R.A., see Zallen 114 (1989) 795
Saito, M., see Imamura 114 (1989) 121
Sakai, H., see Asano 114 (1989) 175
Sakai, H., see Asano 114 (1989) 268
Saleh, Z.M., G.A. Williams and P.C. Taylor, ^{63}Cu NMR studies of the local structural order in the Cu–As–S and Cu–As–Se systems 114 (1989) 58
Salmon, P.S., see Penfold 114 (1989) 82
Santos, M., see Martins 114 (1989) 486
Santos, P.V. and H.J. Trodahl, Phonons in a-Si : H-based amorphous superlattices 114 (1989) 765
Santos-Filho, P., M.P. Volz, R.L. Corey, Y.W. Kim, P.A. Fedders, R.E. Norberg, W. Turner and W. Paul, Molecular HD and D_2 in amorphous semiconductors 114 (1989) 235
Santos-Filho, P., see Bodart 114 (1989) 825
Sasaki, H., see Shimizu 114 (1989) 648
Sasaki, H., M. Deguchi, K. Sate and M. Aiga, High resolution electron energy loss study on the surface of a-$Si_{1-x}Ge_x$: H 114 (1989) 672
Sate, K., see Sasaki 114 (1989) 672
Sauer, B., see Ott 114 (1989) 828
Sauvain, E., see Shah 114 (1989) 402
Saxena, N., D.E. Albright, C.M. Fortmann, T.W.F. Russell, P.M. Fauchet and I.H. Campbell, Temperature dependence of H radical etching in the deposition of microcrystalline silicon alloy thin films by Hg-sensitized photo-CVD 114 (1989) 801
Sayama, K., see Nishikuni 114 (1989) 181
Sayers, D., see Tsu 114 (1989) 199
Sayers, D.E., see Zhou 114 (1989) 43
Sayers, D.E., see Lee 114 (1989) 52
Sayers, D.E., see Yang 114 (1989) 67
Schiff, E.A., see Hotaling 114 (1989) 420

Schiff, E.A., see Lee 114 (1989) 423
Schiff, E.A., see Devlen 114 (1989) 567
Schiff, E.A., see Chen 114 (1989) 585
Schiff, E.A., see Zafar 114 (1989) 618
Schneider, U., B. Schröder and F. Finger, Saturation effect and annealing behaviour of metastable defects induced by keV-electron irradiation in intrinsic a-Si : H 114 (1989) 633
Schreiber, M., see Kramer 114 (1989) 330
Schröder, B., see Schneider 114 (1989) 633
Schroeder, B., see Martin 114 (1989) 537
Schubert, M.B., H.C. Weller, K. Eberhardt and G.H. Bauer, Structural properties of a-$Si_{1-x}Ge_x$: H 114 (1989) 528
Schumacher, R. and P. Thomas, Monte Carlo simulation of low temperature band tail hopping mobility in a-Si : H 114 (1989) 333
Schumm, G. and G.H. Bauer, Defect structure and stability of a-Si : H by modulated photocurrent studies 114 (1989) 660
Schütte, S., F. Finger and W. Fuhs, Effect of electron bombardment and annealing on the hyperfine structure in a-Si : H (P) 114 (1989) 411
Searle, T.M., W.A. Jackson and S. Kalbitzer, Photoluminescence studies of ion implantation damage in a-Si : H 114 (1989) 286
Seibert, K., see Esser 114 (1989) 573
Seibert, K., see Davidson 114 (1989) 579
Seleznev, V.N., see Domashevskaya 114 (1989) 495
Senemaud, C., see Chahed 114 (1989) 471
Senemaud, C., see Driss Khodja 114 (1989) 498
Shah, A.V., E. Sauvain and J. Hubin, Characteristic lengths for transport in illuminated intrinsic a-Si : H 114 (1989) 402
Shao, W.-L., J. Shinar, S. Mitra, B.C. Gerstein, F. Li, J. Fortner and J.S. Lannin, NMR and short range order in amorphous silicon 114 (1989) 232
Shaoqi, P., see Guang 114 (1989) 576
Shapiro, F.R. and M. Silver, Simulation of the effects of capture rates and band mobility on transient currents in a-Si : H pin devices 114 (1989) 351
Shebanin, A.P., see Kudoyarova 114 (1989) 205
Shen, D. and P.K. Bhat, New results on low level phosphorous doping in a-Si : H 114 (1989) 265
Shernyakov, Yu.M., see Vassilyev 114 (1989) 507
Shimakawa, K., T. Okada and O. Imagawa, Electronic transport in organic amorphous polysilanes 114 (1989) 345
Shimakawa, K. and T. Kameyama, Multiphonon hopping of π electrons in amorphous carbons 114 (1989) 786
Shimizu, H., S. Nakao, H. Kusakabe and M. Noda, Microstructures of hydrogenated amorphous carbon films prepared by RF plasma CVD 114 (1989) 196
Shimizu, I., Chemical reactions for propagation of Si-network 114 (1989) 145
Shimizu, I., see Hanna 114 (1989) 172
Shimizu, I., see Hanna 114 (1989) 804
Shimizu, I., see Shirai 114 (1989) 810
Shimizu, T., see Kumeda 114 (1989) 516
Shimizu, T., H. Kidoh, M. Matsumoto, A. Morimoto and M. Kumeda, Photo-created defects in a-Si : H as elucidated by ESR; LESR and CPM 114 (1989) 630
Shimizu, T., X. Xu, H. Sasaki, A. Morimoto and M. Kumeda, Thermal equilibration in hydrogenated amorphous silicon-based films 114 (1989) 648
Shinar, J., see Shinar 114 (1989) 220
Shinar, J., see Shao 114 (1989) 232
Shinar, R., S. Mitra, X.-L. Wu and J. Shinar, Hydrogen diffusion and relaxation processes in a-Si : H and a-Ge : H 114 (1989) 220
Shirafuji, J., see Hattori 114 (1989) 711
Shirai, H., see Hanna 114 (1989) 804
Shirai, H., H. Tanabe, T. Uematsu, J. Hanna and I. Shimizu, Growth of amorphous; microcrystalline and epitaxial silicon at the same substrate temperature under control of atomic hydrogen 114 (1989) 810
Shklovskii, B.I., H. Fritzsche and S.D. Baranovskii, Recombination and photoconductivity in amorphous semiconductors at low temperatures 114 (1989) 325
Shroder, R.E., see Nemanich 114 (1989) 813
Shvarts, K., see Stradins 114 (1989) 79
Siebke, F., W. Beyer, J. Herion and H. Wagner, The prefactor of DC conductivity for amorphous silicon determined by combined contact potential difference and conductivity measurements 114 (1989) 357
Siefert, J.-M., In-situ determination of surface states in undoped and doped a-Si : H 114 (1989) 744
Silver, M., G. Winborne, H. Branz, L. Pautmeier and H. Bassler, A unified model for exponential band tails; optoelectronic properties and metastability in a-Si : H based on charged dangling bonds 114 (1989) 244
Silver, M., see Shapiro 114 (1989) 351
Silver, M., see Branz 114 (1989) 639
Simon, M., see Berner 114 (1989) 678
Šimůnek, A., see Wiech 114 (1989) 492
Singh, A., E.A. Davis and S.C. Bayliss, The effect of hydrogenation on the optical bandgaps of a-SiO_x : H_y thin films 114 (1989) 504
Šípek, E., see Kočka 114 (1989) 336
Šípek, E., see Vaněček 114 (1989) 447
Situ, H., see Jung 114 (1989) 55
Slinger, C.W., see Zakery 114 (1989) 109
Smith, F.W., see Yin 114 (1989) 459
Smith, F.W., see Yin 114 (1989) 489

Smith, Z.E., A. Matsuda, H. Matsuura, H. Oheda, M. Tanaka and S. Yokoyama, Structure; defect and transport properties of highly photoconductive a-SiGe : H and a-SiC : H alloys 114 (1989) 480
Sokolov, A.P., see Malinovsky 114 (1989) 61
Sokolov, A.P., see Kudoyarova 114 (1989) 205
Song, Y.-H., B.-S. Yoo, C. Lee and J. Jang, Thermal equilibrium process in hydrogenated amorphous silicon npnp doping-modulated superlattices 114 (1989) 666
Sopka, J. and H. Oechsner, Determination of hydrogen concentration depth profiles in a-Si : H by secondary neutral mass spectrometry (SNMS) 114 (1989) 208
Sotiropoulos, J. and W. Fuhs, Electronic structure of bismuth modified a-Ge_{25}-$Se_{75-x}Bi_x$ films 114 (1989) 97
Štich, I., see Buda 114 (1989) 7
Štika, O., see Kočka 114 (1989) 336
Stolka, M., see Abkowitz 114 (1989) 342
Stradins, P., K. Shvarts and J. Teteris, The relation of photo and thermal components of photoinduced changes in amorphous semiconductors 114 (1989) 79
Street, R.A., see Johnson 114 (1989) 169
Street, R.A., see Quereshi 114 (1989) 417
Street, R.A. and K. Winer, The influence of growth conditions on the equilibrium states in a-Si : H 114 (1989) 645
Street, R.A., see Winer 114 (1989) 654
Stutzmann, M., see Boyce 114 (1989) 211
Stutzmann, M., Metal impurities in a-Si : H and other amorphous semiconductors 114 (1989) 414
Stutzmann, M., see Aljishi 114 (1989) 462
Sugimoto, H., see Imamura 114 (1989) 121
Sugimura, A., see Naito 114 (1989) 112
Susman, S., see Dejus 114 (1989) 37
Szafranek, I., see Maley 114 (1989) 163

Tada, T. and T. Ninomiya, Photoluminescence from optically induced metastable states in a-As_2S_3 114 (1989) 88
Tagliaferro, A., see Demichelis 114 (1989) 468
Takahama, T., see Nishikuni 114 (1989) 181
Takahashi, T., see Nakayama 114 (1989) 747
Takasaki, Y., see Tsuji 114 (1989) 94
Taketoshi, K., see Tsuji 114 (1989) 94
Tanabe, H., see Shirai 114 (1989) 810
Tanaka, K., Anisotropic amorphous semiconductors – uniaxial compression and squeezing 114 (1989) 31
Tanaka, K., see Okushi 114 (1989) 669
Tanaka, K., see Honma 114 (1989) 726
Tanaka, M., see Smith 114 (1989) 480
Tang, W., see Liu 114 (1989) 738
Tanguy, C., see Fauchet 114 (1989) 564
Tanguy, C., see Mourchid 114 (1989) 582
Tauc, J., see Devlen 114 (1989) 289
Tauc, J., see Zhou 114 (1989) 292
Tauc, J., see Devlen 114 (1989) 567
Tauc, J., see Chen 114 (1989) 585
Taylor, P.C., see Liu 114 (1989) 25
Taylor, P.C., see Saleh 114 (1989) 58
Taylor, P.C., see Hautala 114 (1989) 85
Taylor, P.C., see Ristein 114 (1989) 91
Taylor, P.C., see Ristein 114 (1989) 444
Terekhov, V.A., see Domashevskaya 114 (1989) 495
Terukov, E.I., see Kudoyarova 114 (1989) 205
Terukov, E.I., see Vassilyev 114 (1989) 507
Teteris, J., see Stradins 114 (1989) 79
Theye, M.L., see Chahed 114 (1989) 471
Theye, M.L., see Driss Khodja 114 (1989) 498
Thèye, M.-L., see Zallen 114 (1989) 795
Thomas, P., see Schumacher 114 (1989) 333
Thompson, R., see Tsai 114 (1989) 151
Thompson, R., see Jackson 114 (1989) 396
Thorpe, M.F. and Y. Cai, Mechanical and vibrational properties of network structures 114 (1989) 19
Thorton, J.A., see Maley 114 (1989) 163
Tikhomirov, V.K., see Lyubin 114 (1989) 133
Timoshenko, Yu.K., see Domashevskaya 114 (1989) 495
Tong, B.Y., see Du 114 (1989) 369
Toyoshima, Y., K. Arai and A. Matsuda, Lattice orientation of microcrystallites in μc-Si : H 114 (1989) 819
Třiska, A., see Vaněček 114 (1989) 447
Trodahl, H.J., see Santos 114 (1989) 765
Tsai, C.C., G.B. Anderson, R. Thompson and B. Wacker, Control of silicon network structure in plasma deposition 114 (1989) 151
Tsai, C.C., see Jackson 114 (1989) 396
Tsendin, K.D., Charge carrier statistics of disordered semiconductors with negative-U defects and electrically active impurity atoms 114 (1989) 118
Tsu, D.V., see Yin 114 (1989) 459
Tsu, D.V. and G. Lucovsky, SiH stretching vibration in silicon suboxides: local and remote induction effects 114 (1989) 501
Tsu, R., M.A. Paesler and D. Sayers, Phonon linewidth and bond angle deviation in amorphous silicon and germanium 114 (1989) 199
Tsu, R., Phase coherence and damping in amorphous quantum wells 114 (1989) 708
Tsuda, S., see Nishikuni 114 (1989) 181
Tsuji, K., Y. Takasaki, T. Hirai and K. Taketoshi, Impact ionization process in amorphous selenium 114 (1989) 94
Tsuo, Y.S., see Galloni 114 (1989) 271
Tsutsumi, Y., K. Uchiyama, H. Okamoto and Y. Hamakawa, Light-induced changes in the deep states of undoped a-Si : H 114 (1989) 627

Turner, W., see Santos-Filho 114 (1989) 235
Turner, W.A., see Jones 114 (1989) 525

Uchiyama, K., see Tsutsumi 114 (1989) 627
Uematsu, T., see Shirai 114 (1989) 810
Unold, T. and J.D. Cohen, The carbon impurity dependence of light induced metastable effects in hydrogenated amorphous silicon 114 (1989) 603

Vanderhaghen, R. and C. Longeaud, Influence of the incorporation of germanium on the tail states in amorphous alloys semiconductors 114 (1989) 540
Vanderhaghen, R., see Fauchet 114 (1989) 564
Vanderhaghen, R., see Mourchid 114 (1989) 582
Vanecek, M., see Favre 114 (1989) 405
Vaněček, M., J. Kočka, E. Šípek and A. Tříska, On mobility–lifetime problem and on quantum efficiency of photogeneration in amorphous silicon 114 (1989) 447
Vardeny, Z., see Devlen 114 (1989) 289
Vardeny, Z., see Han 114 (1989) 588
Vardeny, Z.V., see Zhou 114 (1989) 292
Vassilyev, V.A., A.S. Volkov, E. Musabekov, E.I. Terukov, S.V. Chernyshov and Yu. M. Shernyakov, Photoluminescence of amorphous hydrogenated silicon–carbon (a-SiC : H) films 114 (1989) 507
Vateva, E. and I. Georgieva, Amorphous Se/Se–Te multilayers 114 (1989) 124
Verrall, D.J. and S.R. Elliott, Structure of phosphorus selenide glasses 114 (1989) 34
Vieira, M., see Martins 114 (1989) 486
Vikhrov, S.P., see Aivazov 114 (1989) 157
Volin, K.J., see Dejus 114 (1989) 37
Volkov, A.S., see Vassilyev 114 (1989) 507
Volz, M.P., see Santos-Filho 114 (1989) 235
Volz, M.P., P.A. Fedders and R.E. Norberg, Deuteron magnetic resonance in amorphous germanium 114 (1989) 546
Vomvas, A., see Johanson 114 (1989) 274

Wacker, B., see Tsai 114 (1989) 151
Wagner, H., see Horbach 114 (1989) 187
Wagner, H., see Beyer 114 (1989) 217
Wagner, H., see Siebke 114 (1989) 357
Wagner, P., see Gelatos 114 (1989) 699
Wagner, S., see Roca i Cabarrocas 114 (1989) 190
Wagner, S., see Liu 114 (1989) 363
Wagner, S., V. Chu, J.P. Conde and J.Z. Liu, The optoelectronic properties of a-Si;Ge : H(F) alloys 114 (1989) 453
Wagner, S., see Conde 114 (1989) 693
Wagner, S., see Okada 114 (1989) 816
Wakayama, Y., see Arai 114 (1989) 40
Walker, J., see Johnson 114 (1989) 169
Wang, C., see Lucovsky 114 (1989) 154
Wang, C., see Parsons 114 (1989) 178
Wang, C., G.N. Parsons and G. Lucovsky, Effects of gas additives on the properties of a-Si : H films 114 (1989) 193
Wang, C., see Esser 114 (1989) 573
Wang, C., see Nemanich 114 (1989) 813
Wang, S. and R. Cheng, Interface defect density in a-Si : H/a-SiN_x : H multilayers 114 (1989) 702
Wang, S., H. Fritzsche and R. Cheng, Annealing dependence of PDS of a-Si : H/a-SiN_x : H multilayers 114 (1989) 741
Wang, Z., see Liu 114 (1989) 738
Wang, Z.T., see Jung 114 (1989) 55
Watanabe, K., see Nakayama 114 (1989) 747
Weaire, D., see Wooten 114 (1989) 681
Wei, G.-P., D. Kruangam, T. Endo, H. Okamoto and Y. Hamakawa, Measurement of the energy band discontinuities in a-SiC p-i-n junctions by internal photoemission 114 (1989) 735
Wei, X., see Han 114 (1989) 588
Weiser, G., see Ristein 114 (1989) 91
Weiser, G., Evidence for energy dependent optical matrix elements in the electroabsorption spectra of amorphous semiconductors 114 (1989) 250
Weiser, G. and H. Mell, Temperature dependence of the optical absorption edge in a-Si : H 114 (1989) 298
Weiser, G., see Wiech 114 (1989) 483
Weiser, G., see Wiech 114 (1989) 492
Weller, H.C., see Schubert 114 (1989) 528
Werner, A., see Neitzert 114 (1989) 166
Wiech, G., W. Zahorowsky and G. Weiser, Local bonding of Si in $Si_{1-x}C_x$ alloys studied by X-ray emission 114 (1989) 483
Wiech, G., W. Zahorowski, A. Šimůnek, H. Mell and G. Weiser, Si K-emission bands of nitrogen rich a-SiN_x : H 114 (1989) 492
Willeke, G., see Martins 114 (1989) 486
Williams, G.A., see Saleh 114 (1989) 58
Williams, M.J., see Parsons 114 (1989) 178
Williamson, D.L., A.H. Mahan, B.P. Nelson and R.S. Crandall, The observation of microvoids in device quality hydrogenated amorphous silicon 114 (1989) 226
Winborne, G., see Silver 114 (1989) 244
Wind, J., G. Krötz, V. Petrova-Koch, G. Müller and P.P. Deimel, Structural and electronic properties of doped a-Si_{1-x}-Ge_x : H alloys grown with H-dilution 114 (1989) 531
Wind, J., see Krötz 114 (1989) 663
Winer, K., see Johnson 114 (1989) 169
Winer, K., see Street 114 (1989) 645
Winer, K. and R.A. Street, Arsenic incorporation in a-Si : H 114 (1989) 654

Wong, H.K., see Ong 114 (1989) 783
Wong, S.K., see Du 114 (1989) 369
Wooten, F. and D. Weaire, A computer-generated model of the crystalline/amorphous interface in silicon 114 (1989) 681
Wronski, C.R., see Lee 114 (1989) 316
Wu, L., D. Han and J.I. Pankove, Excess optical absorption in a-Si:H after illumination with bandgap light 114 (1989) 606
Wu, X.-L., see Shinar 114 (1989) 220
Wu, Y.-J., see Persans 114 (1989) 771

Xia, H., see Chen 114 (1989) 780
Xiao, Y. and D. Han, Optical absorption spectra in a-Si:H measured by PDS and CPM in situ 114 (1989) 438
Xin, Y.Z., see Guang 114 (1989) 576
Xu, X., see Shimizu 114 (1989) 648

Yadav, P.S., see Agrawal 114 (1989) 519
Yamada, K., see Hazama 114 (1989) 777
Yamaguchi, M., Y. Fujita and K. Morigaki, Photoluminescence of a-$Si_{1-x}Au_x$:H films: nonradiative nature of Au centers 114 (1989) 283
Yamaguchi, M., see Yoshida 114 (1989) 319
Yamaguchi, M., C. Ogihara, H. Ohta and K. Morigaki, Optical properties of band-edge modulated a-$Si_{1-x}N_x$:H films 114 (1989) 705
Yamasaki, S., see Hautala 114 (1989) 85
Yang, C.Y., D.E. Sayers and M.A. Paesler, Local bonding configurations of amorphous Se_xTe_{1-x} films 114 (1989) 67
Yannacopoulos, S., see Kasap 114 (1989) 49
Yannacopoulos, S., see Kasap 114 (1989) 106
Yin, Z., D.V. Tsu, G. Lucovsky and F.W. Smith, Annealing study of the infrared absorption in an amorphous silicon dioxide film 114 (1989) 459
Yin, Z. and F.W. Smith, Microstructure of nitrogen-rich a-$Si_xN_yH_z$ films 114 (1989) 489
Yokomichi, H., M. Kondo and K. Morigaki, Electron-nuclear double resonance of dangling-bond centres in a-$Si_{1-x}N_x$:H and a-$Si_{1-x}N_x$ 114 (1989) 426
Yokoyama, S., see Smith 114 (1989) 480
Yoo, B.-S., see Song 114 (1989) 666
Yoon, J.-W., M.-S. Kim and C. Lee, Light-induced conductivity changes in phosphorus-doped hydrogenated amorphous silicon 114 (1989) 636
Yoshida, M., M. Yamaguchi and K. Morigaki, Nature of triplet excitons in a-Si:H; its alloys and a-Si:H/a-Si_3;N_4:H multilayers as elucidated by optically detected magnetic resonance measurements 114 (1989) 319
Yu, G., G. Chen and F. Zhang, Computer simulation of effects of hydrogen on the dangling bonds in hydrogenated amorphous silicon 114 (1989) 429
Yu, R.Q., see Fortner 114 (1989) 675

Zafar, S. and E.A. Schiff, Temperature-dependent defect density measurements in hydrogenated amorphous silicon 114 (1989) 618
Zahorowski, W., see Wiech 114 (1989) 492
Zahorowsky, W., see Wiech 114 (1989) 483
Zakery, A., A. Zekak, P.J.S. Ewen, C.W. Slinger and A.E. Owen, Optical constants of Ag-photodoped As–S amorphous films 114 (1989) 109
Zallen, R., M. Holtz, A.E. Geissberger, R.A. Sadler, W. Paul and M.-L. Thèye, Raman-scattering studies of implantation-amorphized gallium arsenide: comparison to sputtered and evaporated a-GaAs films 114 (1989) 795
Zdetsis, A.D., A complete bonding and banding study of amorphous α-SiC and α-SiC:H alloys 114 (1989) 513
Zekak, A., see Zakery 114 (1989) 109
Zhang, F., see Yu 114 (1989) 429
Zhang, F., see He 114 (1989) 657
Zhang, Z., M. Qi, J. Chen and R. Cheng, Stress in a-$Si_{1-x}C_x$:H studied by (n;-n) double crystal diffractometry 114 (1989) 510
Zhao, Z., see Liu 114 (1989) 738
Zhou, T.X., J. Tauc and Z.V. Vardeny, Transient photomodulation studies of phosphorus doped a-Si:H 114 (1989) 292
Zhou, T.X., see Fortmann 114 (1989) 624
Zhou, W., J.M. Lee, D.E. Sayers and M.A. Paesler, An EXAFS study of compositional trends and photo-induced structural changes in amorphous As_xS_{1-x} thin films 114 (1989) 43
Zhou, W.H., see Guang 114 (1989) 576
Zhu, Y.T., see Du 114 (1989) 369
Zignani, F., see Galloni 114 (1989) 271
Zitkovsky, I. and P. Boolchand, Molecular structure of As_2S_3 glass 114 (1989) 70

Journal of Non-Crystalline Solids 114 (1989) 845–854
North-Holland

SUBJECT INDEX

Absorption
Defects, Silicon Alloys 114 (1989) 702
Silicon, Density of States 114 (1989) 298

Aerogels
Alloys, Optical Properties, X-ray Absorption 114 (1989) 471

Alloys
Aerogels, Optical Properties, X-ray Absorption 114 (1989) 471
Chalcogenides, Differential Thermal Analysis, Glass Transition 114 (1989) 46
Chalcogenides, EXAFS 114 (1989) 67
Chalcogenides, Photoinduced Effects 114 (1989) 76
Defects 114 (1989) 558
Defects, Silicon Alloys 114 (1989) 462
Deposition Techniques, Carbon 114 (1989) 468
Electron Spin Resonance 114 (1989) 657
Germania 114 (1989) 732
Hydrogenation 114 (1989) 519
Infra-red Absorption 114 (1989) 561
Luminescence, Recombination 114 (1989) 283
MultiLayers, Growth Kinetics 114 (1989) 726
Silicon, Luminescence, Recombination, Silicon Alloys 114 (1989) 280
Silicon, Nuclear Magnetic Resonance 114 (1989) 426
Silicon, Structure 114 (1989) 13
Silicon, Time-Resolved Spectroscopy 114 (1989) 582
Silicon Alloys 114 (1989) 672
Silicon Alloys, Deposition Techniques 114 (1989) 807
Stress Measurement, Silicon Alloys 114 (1989) 510
Time-Resolved Spectroscopy 114 (1989) 588

Amorphous Solids
Computer Simulation, Photoresponse 114 (1989) 339
Dangling Bonds 114 (1989) 393
Diffusion, Hydrogenation 114 (1989) 396
Hall Coefficient, Transport Properties – Solids 114 (1989) 369
Hall Coefficient, Transport Properties – Solids 114 (1989) 372
III–V semiconductors, Raman Spectra, Ion Implantation, Sputtering 114 (1989) 795
Mobility, Photoconductivity 114 (1989) 336
Mobility, Silicon, Density of States 114 (1989) 354
Noise, Capacitance Methods 114 (1989) 696
Optical Properties, Silicon 114 (1989) 687
Photoconductivity, Hopping, Recombination 114 (1989) 325
Photomodulation, Density 114 (1989) 378
Recombination, Carbon, Electron Spin Resonance 114 (1989) 310
Thermoelectric Power 114 (1989) 375
Transport Properties – Solids 114 (1989) 348
Transport Properties – Solids 114 (1989) 357
Transport Properties – Solids 114 (1989) 360
Transport Properties – Solids, Photoconductivity, Silicon 114 (1989) 345

Bonding
Liquid Semiconductors, Theory 114 (1989) 828
Silicon Alloys, Density of States, X-ray Emission 114 (1989) 483

Boron
Coatings 114 (1989) 783

Capacitance Methods
Density of States, Defects, Silicon, Hydrogenation, Ion Implantation 114 (1989) 381
Electron Spin Resonance, Silicon, Hydrogenation, Defects 114 (1989) 435
Noise, Amorphous Solids 114 (1989) 696
Silicon, Silica 114 (1989) 699
Stäbler–Wronski Effect 114 (1989) 603

Carbon
Alloys, Deposition Techniques 114 (1989) 468
Hopping, Transport Properties – Solids 114 (1989) 786
Recombination, Amorphous Solids, Electron Spin Resonance 114 (1989) 310

Chalcogenides
Alloys, Differential Thermal Analysis, Glass Transition 114 (1989) 46
Chemical Modification, Transient Effects 114 (1989) 100
Computer Simulation, EXAFS 114 (1989) 73
Electric Properties 114 (1989) 85
Electric Properties, Luminescence 114 (1989) 88
EXAFS, Alloys 114 (1989) 67
EXAFS, Photoinduced Effects 114 (1989) 43
Hall Coefficient 114 (1989) 82
Hall Coefficient, Structure, EXAFS, Raman Spectra 114 (1989) 34
Heat Capacity 114 (1989) 58
Heat Capacity 114 (1989) 91
Ion Implantation, Recombination 114 (1989) 94

0022-3093/89/$03.50 © Elsevier Science Publishers B.V.
(North-Holland)

Mössbauer Effect 114 (1989) 70
MultiLayers 114 (1989) 121
MultiLayers 114 (1989) 124
Optical Properties 114 (1989) 136
Optical Properties, Thin Films 114 (1989) 109
Photoinduced Effects 114 (1989) 55
Photoinduced Effects 114 (1989) 79
Photoinduced Effects, Alloys 114 (1989) 76
Photoinduced Effects, Computer Simulation 114 (1989) 52
Photoinduced Effects, Optical Properties 114 (1989) 127
Photoinduced Effects, Rutherford Backscattering 114 (1989) 40
Photoinduced Effects, Theory, Optical Properties 114 (1989) 304
Pressure Effects 114 (1989) 31
Pressure Effects, Optical Properties 114 (1989) 130
Raman Spectra, Mössbauer Effect, Pressure Effects 114 (1989) 64
Silicon, Defects 114 (1989) 118
Structure 114 (1989) 115
Thin Films, Photoinduced Effects 114 (1989) 133
Transient Effects 114 (1989) 112
Transport Properties – Solids, Mobility, Differential Thermal Analysis, Glass Transition 114 (1989) 49
Transport Properties – Solids, Photoconductivity 114 (1989) 106

Chemical Modification
Chalcogenides, Transient Effects 114 (1989) 100

Coatings
Boron 114 (1989) 783

Computer Simulation
Chalcogenides, EXAFS 114 (1989) 73
Chalcogenides, Photoinduced Effects 114 (1989) 52
Hopping, Density of States, Silicon 114 (1989) 333
Mobility, Diodes 114 (1989) 351
Photoresponse, Amorphous Solids 114 (1989) 339

Crystallization
Silicon, Silicon Alloys, Heat Capacity, Hydrogenation 114 (1989) 211
Silicon, X-ray Diffraction 114 (1989) 819

Dangling Bonds
Amorphous Solids 114 (1989) 393
Recombination, Silicon 114 (1989) 441
Silicon, Electronic Structure 114 (1989) 244
Silicon, Transistors, Thin Film Transistors 114 (1989) 642

Defects
Alloys 114 (1989) 558
Alloys, Silicon Alloys 114 (1989) 462
Chalcogenides, Silicon 114 (1989) 118
Density of States, Silicon, Hydrogenation, Capacitance Methods, Ion Implantation 114 (1989) 381
Deposition Techniques, Germania, Glow Discharge, Transport Properties – Solids 114 (1989) 477
Doping, Silicon Alloys 114 (1989) 268
Electron Spin Resonance 114 (1989) 618
Electron Spin Resonance 114 (1989) 648
Electron Spin Resonance, Capacitance Methods, Silicon, Hydrogenation 114 (1989) 435
Electron Spin Resonance, Silicon, Photoconductivity 114 (1989) 630
Luminescence 114 (1989) 444
Mobility, Silicon 114 (1989) 420
Photoconductivity, Silicon 114 (1989) 660
Recombination, Electronic Structure, Silicon Alloys 114 (1989) 387
Silicon 114 (1989) 178
Silicon 114 (1989) 597
Silicon 114 (1989) 600
Silicon 114 (1989) 627
Silicon 114 (1989) 633
Silicon, Electronic Structure 114 (1989) 405
Silicon, Kinetics 114 (1989) 591
Silicon, Optical Properties 114 (1989) 609
Silicon, Optical Properties 114 (1989) 738
Silicon, Transport Properties – Solids 114 (1989) 639
Silicon, Trapping 114 (1989) 615
Silicon Alloys, Absorption 114 (1989) 702
Silicon Alloys, Kinetics 114 (1989) 621
Silicon Alloys, Surface Properties 114 (1989) 750
Silicon Alloys, Transport Properties – Solids, Photoconductivity 114 (1989) 480
X-ray Absorption, Silicon 114 (1989) 223

Density
Photomodulation, Amorphous Solids 114 (1989) 378

Density of States
Absorption, Silicon 114 (1989) 298
Defects, Silicon, Hydrogenation, Capacitance Methods, Ion Implantation 114 (1989) 381
Hopping, Computer Simulation, Silicon 114 (1989) 333
Mobility, Amorphous Solids, Silicon 114 (1989) 354
Optical Properties 114 (1989) 438
Secondary Electron Emission 114 (1989) 432
Silicon, Electronic Structure 114 (1989) 651
Silicon, Photoconductivity 114 (1989) 450
Silicon Alloys, Bonding, X-ray Emission 114 (1989) 483

Deposition Techniques
Alloys, Carbon 114 (1989) 468
Alloys, Silicon Alloys 114 (1989) 807
Germania, Glow Discharge, Defects, Transport Properties – Solids 114 (1989) 477
Silicon 114 (1989) 145
Silicon 114 (1989) 187
Silicon 114 (1989) 193
Silicon 114 (1989) 196
Silicon, Infra-red Absorption 114 (1989) 154
Silicon Alloys, Raman Spectra 114 (1989) 528

Devices
Silicon 114 (1989) 417

Dielectric Properties
Microstructure, Silicon Nitride, Infra-red Absorption 114 (1989) 489
Raman Spectra 114 (1989) 813

Differential Thermal Analysis
Chalcogenides, Alloys, Glass Transition 114 (1989) 46
Chalcogenides, Transport Properties – Solids, Mobility, Glass Transition 114 (1989) 49

Diffusion
Amorphous Solids, Hydrogenation 114 (1989) 396
Hydrogen Effects, Silicon 114 (1989) 220
Surface Reactions 114 (1989) 217

Diodes
Mobility, Computer Simulation 114 (1989) 351

Doping
Defects, Silicon Alloys 114 (1989) 268
Photoconductivity 114 (1989) 265
Photomodulation, Silicon 114 (1989) 292
Silicon 114 (1989) 654
Silicon, Field Effect 114 (1989) 663
Silicon, Growth Kinetics 114 (1989) 169
Silicon, Ion Implantation 114 (1989) 271
Silicon, Metastability 114 (1989) 669
Silicon, MultiLayers 114 (1989) 666
Silicon, Photoinduced Effects 114 (1989) 289

Elastic Properties
Mechanical Properties, Structure 114 (1989) 19

Electric Properties
Chalcogenides 114 (1989) 85
Chalcogenides, Luminescence 114 (1989) 88
Microstructure, Transport Properties – Solids, Optical Properties 114 (1989) 486

Electrical Properties
Silicon, MultiLayers 114 (1989) 301

Electrical Properties and Relaxation
Silicon Alloys, Optical Properties 114 (1989) 789

Electroabsorption
Silicon, Electronic Structure 114 (1989) 250

Electron Microscopy
Glass Formation 114 (1989) 465

Electron Spin Resonance
Alloys 114 (1989) 657
Capacitance Methods, Silicon, Hydrogenation, Defects 114 (1989) 435
Defects 114 (1989) 618
Defects 114 (1989) 648
Photoinduced Effects 114 (1989) 612
Recombination, Amorphous Solids, Carbon 114 (1989) 310
Silicon 114 (1989) 411
Silicon 114 (1989) 414
Silicon 114 (1989) 729
Silicon, Defects, Photoconductivity 114 (1989) 630
Silicon Alloys 114 (1989) 423
Silicon Alloys 114 (1989) 585
Silicon Alloys, Recombination 114 (1989) 549

Electronic Conductivity
Silicon, Silicon Nitride, MultiLayers, Transport Properties – Solids 114 (1989) 759
Silicon Alloys, MultiLayers, Transport Properties – Solids 114 (1989) 762

Electronic Structure
Defects, Recombination, Silicon Alloys 114 (1989) 387
Silicon 114 (1989) 238
Silicon 114 (1989) 247
Silicon, Dangling Bonds 114 (1989) 244
Silicon, Defects 114 (1989) 405
Silicon, Density of States 114 (1989) 651
Silicon, Electroabsorption 114 (1989) 250
Silicon Alloys, Silicon Nitride, XPS 114 (1989) 498
Theory 114 (1989) 253
Theory 114 (1989) 256
Theory, Silicon, Gap States 114 (1989) 262
Transient Effects 114 (1989) 259

Ellipsometry
Silicon 114 (1989) 139
Silicon 114 (1989) 160

EXAFS
Chalcogenides, Alloys 114 (1989) 67
Chalcogenides, Computer Simulation 114 (1989) 73
Chalcogenides, Hall Coefficient, Structure, Raman Spectra 114 (1989) 34
Chalcogenides, Photoinduced Effects 114 (1989) 43
Silicon 114 (1989) 229

Fermi Level
Silicon Alloys, Surface Reactions 114 (1989) 744

Field Effect
Silicon, Doping 114 (1989) 663

Fluorides
Growth Kinetics, Silicon 114 (1989) 816
Silicon Alloys 114 (1989) 453

Gallium Phosphide
Mobility, Hydrogen Effects 114 (1989) 792

Gap States
Theory, Silicon, Electronic Structure 114 (1989) 262

Germania
Alloys 114 (1989) 732
Deposition Techniques, Glow Discharge, Defects, Transport Properties – Solids 114 (1989) 477
Silicon, Phonons 114 (1989) 199
Theory 114 (1989) 708

Germanium
Hydrogenation 114 (1989) 798
Liquid Semiconductors, Silicon 114 (1989) 16
Microstructure 114 (1989) 546
Nuclear Magnetic Resonance, Silicon 114 (1989) 235
Raman Spectra, Microstructure, Surface Properties 114 (1989) 675
Structure, Hydrogenation 114 (1989) 525

Glass Formation
Electron Microscopy 114 (1989) 465

Glass Transition
Chalcogenides, Alloys, Differential Thermal Analysis 114 (1989) 46
Chalcogenides, Transport Properties – Solids, Mobility, Differential Thermal Analysis 114 (1989) 49

Glow Discharge
Deposition Techniques, Germania, Defects, Transport Properties – Solids 114 (1989) 477
Silicon, Growth Kinetics, Optical Properties 114 (1989) 190

Growth Kinetics
MultiLayers, Alloys 114 (1989) 726
Silicon 114 (1989) 172
Silicon 114 (1989) 184
Silicon 114 (1989) 645
Silicon, Doping 114 (1989) 169
Silicon, Fluorides 114 (1989) 816
Silicon, Hydrogen Effects 114 (1989) 810
Silicon, Kinetics 114 (1989) 166
Silicon, Optical Properties, Glow Discharge 114 (1989) 190
Silicon, Theory 114 (1989) 157

Hall Coefficient
Amorphous Solids, Transport Properties – Solids 114 (1989) 369
Amorphous Solids, Transport Properties – Solids 114 (1989) 372
Chalcogenides 114 (1989) 82
Chalcogenides, Structure, EXAFS, Raman Spectra 114 (1989) 34
Raman Spectra 114 (1989) 37

Heat Capacity
Chalcogenides 114 (1989) 58
Chalcogenides 114 (1989) 91
Silicon, Silicon Alloys, Hydrogenation, Crystallization 114 (1989) 211

Heterojunctions
Photo-emission 114 (1989) 555
Structure, Silicon Alloys 114 (1989) 756

Hopping
Carbon, Transport Properties – Solids 114 (1989) 786
Computer Simulation, Density of States, Silicon 114 (1989) 333
Photoconductivity, Amorphous Solids, Recombination 114 (1989) 325

Hydrogen Effects
Gallium Phosphide, Mobility 114 (1989) 792
Silicon, Diffusion 114 (1989) 220
Silicon, Growth Kinetics 114 (1989) 810
Silicon, Structure 114 (1989) 208
Silicon Alloys 114 (1989) 804
Silicon Alloys, Transport Properties – Solids 114 (1989) 822

Hydrogenation
Alloys 114 (1989) 519
Density of States, Defects, Silicon, Capacitance Methods, Ion Implantation 114 (1989) 381
Diffusion, Amorphous Solids 114 (1989) 396
Electron Spin Resonance, Capacitance Methods, Silicon, Defects 114 (1989) 435
Germanium 114 (1989) 798
Interfaces, Silicon Alloys 114 (1989) 753
Silicon, Microstructure 114 (1989) 226
Silicon, Photoinduced Effects 114 (1989) 295
Silicon, Silicon Alloys, Heat Capacity, Crystallization 114 (1989) 211
Silicon Alloys, Secondary Ion Mass Spectroscopy, XPS 114 (1989) 474
Structure, Germanium 114 (1989) 525
Thin Films, Optical Properties 114 (1989) 504

III–V semiconductors
Raman Spectra, Ion Implantation, Sputtering, Amorphous Solids 114 (1989) 795

Infra-red Absorption
Alloys 114 (1989) 561
Microstructure, Silicon Nitride, Dielectric Properties 114 (1989) 489
Silicates 114 (1989) 459
Silicon 114 (1989) 163
Silicon, Deposition Techniques 114 (1989) 154
Silicon Alloys 114 (1989) 501

Interfaces
Hydrogenation, Silicon Alloys 114 (1989) 753
MultiLayers 114 (1989) 774
MultiLayers, Silicon Nitride, Localization 114 (1989) 747

Silicon 114 (1989) 684
Superlattices 114 (1989) 777

Ion Implantation
Chalcogenides, Recombination 114 (1989) 94
Density of States, Defects, Silicon, Hydrogenation, Capacitance Methods 114 (1989) 381
III–V semiconductors, Raman Spectra, Sputtering, Amorphous Solids 114 (1989) 795
Luminescence, Silicon 114 (1989) 97
Photoresponse, Photoinduced Effects 114 (1989) 286
Silicon, Doping 114 (1989) 271

Kinetics
Defects, Silicon 114 (1989) 591
Silicon, Growth Kinetics 114 (1989) 166
Silicon Alloys, Defects 114 (1989) 621

Liquid Semiconductors
Bonding, Theory 114 (1989) 828
Silicon, Germanium 114 (1989) 16

Localization
MultiLayers, Interfaces, Silicon Nitride 114 (1989) 747
Theory, Mobility Edge 114 (1989) 330

Luminescence
Alloys, Recombination 114 (1989) 283
Chalcogenides, Electric Properties 114 (1989) 88
Defects 114 (1989) 444
Nuclear Magnetic Resonance, Silicon Alloys 114 (1989) 522
Silicon, Ion Implantation 114 (1989) 97
Silicon, Recombination 114 (1989) 277
Silicon, Recombination, Alloys, Silicon Alloys 114 (1989) 280
Silicon Alloys 114 (1989) 507
Silicon Nitride, Relaxation, Recombination 114 (1989) 570

Magnetic Properties
Silicon Alloys, Photoinduced Effects 114 (1989) 319

Mechanical Properties
Elastic Properties, Structure 114 (1989) 19

Metastability
Doping, Silicon 114 (1989) 669

Microstructure
Germanium 114 (1989) 546
Raman Spectra, Germanium, Surface Properties 114 (1989) 675
Silicon, Hydrogenation 114 (1989) 226
Silicon Nitride, Dielectric Properties, Infrared Absorption 114 (1989) 489
Transport Properties – Solids, Optical Properties, Electric Properties 114 (1989) 486

Mixed-alkali Effect
Transport Properties – Solids, Photo Voltage 114 (1989) 1

Mobility
Amorphous Solids, Photoconductivity 114 (1989) 336
Amorphous Solids, Silicon, Density of States 114 (1989) 354
Chalcogenides, Transport Properties – Solids, Differential Thermal Analysis, Glass Transition 114 (1989) 49
Computer Simulation, Diodes 114 (1989) 351
Gallium Phosphide, Hydrogen Effects 114 (1989) 792
Photoconductivity 114 (1989) 103
Polymers, Transport Properties – Solids 114 (1989) 342
Silicon 114 (1989) 447
Silicon, Defects 114 (1989) 420
Silicon, Transport Properties – Solids 114 (1989) 363
Silicon Alloys, Optical Properties 114 (1989) 564

Mobility Edge
Localization, Theory 114 (1989) 330

Modelling
Silicon 114 (1989) 429
Silicon, Theory 114 (1989) 202

Molecular Dynamics
Semiconductors, Structure 114 (1989) 7

Mössbauer Effect
Chalcogenides 114 (1989) 70
Chalcogenides, Raman Spectra, Pressure Effects 114 (1989) 64

Multilayers
Chalcogenides 114 (1989) 121
Chalcogenides 114 (1989) 124
Electrical Properties, Silicon 114 (1989) 301
Growth Kinetics, Alloys 114 (1989) 726
Interfaces 114 (1989) 774
Interfaces, Silicon Nitride, Localization 114 (1989) 747
Optical Properties, Silicon Nitride, Silicon 114 (1989) 723
Semiconductors 114 (1989) 771
Silicon, Doping 114 (1989) 666
Silicon, Silicon Nitride 114 (1989) 741
Silicon, Silicon Nitride, Transport Properties – Solids, Electronic Conductivity 114 (1989) 759
Silicon Alloys, Transport Properties – Solids, Electronic Conductivity 114 (1989) 762
Time-Resolved Spectroscopy 114 (1989) 576
Transport Properties – Devices 114 (1989) 711

Noise
Amorphous Solids, Capacitance Methods 114 (1989) 696

Nuclear Magnetic Resonance
Alloys, Silicon 114 (1989) 426
Luminescence, Silicon Alloys 114 (1989) 522

Silicon 114 (1989) 232
Silicon 114 (1989) 825
Silicon, Germanium 114 (1989) 235
Silicon, Optical Properties 114 (1989) 408
Silicon Alloys, Silicon Nitride 114 (1989) 516

Optical Properties
Aerogels, Alloys, X-ray Absorption 114 (1989) 471
Chalcogenides 114 (1989) 136
Chalcogenides, Photoinduced Effects, Theory 114 (1989) 304
Chalcogenides, Thin Films 114 (1989) 109
Density of States 114 (1989) 438
Microstructure, Transport Properties – Solids, Electric Properties 114 (1989) 486
MultiLayers, Silicon Nitride, Silicon 114 (1989) 723
Photoinduced Effects, Chalcogenides 114 (1989) 127
Photoinduced Effects, Silicon, Photoresponse, Silicon Alloys 114 (1989) 606
Pressure Effects, Chalcogenides 114 (1989) 130
Raman Spectra, Silicon 114 (1989) 205
Silicon 114 (1989) 579
Silicon, Amorphous Solids 114 (1989) 687
Silicon, Defects 114 (1989) 609
Silicon, Defects 114 (1989) 738
Silicon, Growth Kinetics, Glow Discharge 114 (1989) 190
Silicon, Nuclear Magnetic Resonance 114 (1989) 408
Silicon Alloys 114 (1989) 322
Silicon Alloys 114 (1989) 705
Silicon Alloys, Electrical Properties and Relaxation 114 (1989) 789
Silicon Alloys, Mobility 114 (1989) 564
Thin Films, Hydrogenation 114 (1989) 504

Oxides
Silicon, Surface Properties 114 (1989) 678

Phonons
Silicon, Germania 114 (1989) 199
Superlattices 114 (1989) 765

Photo-emission
Heterojunctions 114 (1989) 555
Silicon Alloys 114 (1989) 735

Photo Voltage
Transport Properties – Solids, Mixed-alkali Effect 114 (1989) 1

Photoconductivity
Amorphous Solids, Hopping, Recombination 114 (1989) 325
Chalcogenides, Transport Properties – Solids 114 (1989) 106
Defects, Silicon 114 (1989) 660
Doping 114 (1989) 265
Electron Spin Resonance, Silicon, Defects 114 (1989) 630
Mobility 114 (1989) 103
Mobility, Amorphous Solids 114 (1989) 336
Recombination, Silicon 114 (1989) 307
Silicon 114 (1989) 714
Silicon 114 (1989) 717
Silicon, Density of States 114 (1989) 450
Silicon, Photoinduced Effects 114 (1989) 316
Silicon, Silicon Alloys 114 (1989) 175
Silicon Alloys, Transport Properties – Solids, Defects 114 (1989) 480
Superlattices 114 (1989) 720
Transport Properties – Solids 114 (1989) 274
Transport Properties – Solids, Amorphous Solids, Silicon 114 (1989) 345

Photoinduced Effects
Chalcogenides 114 (1989) 55
Chalcogenides 114 (1989) 79
Chalcogenides, Alloys 114 (1989) 76
Chalcogenides, Computer Simulation 114 (1989) 52
Chalcogenides, EXAFS 114 (1989) 43
Chalcogenides, Optical Properties 114 (1989) 127
Chalcogenides, Rutherford Backscattering 114 (1989) 40
Chalcogenides, Theory, Optical Properties 114 (1989) 304
Chalcogenides, Thin Films 114 (1989) 133
Doping, Silicon 114 (1989) 289
Electron Spin Resonance 114 (1989) 612
Photoconductivity, Silicon 114 (1989) 316
Photoresponse, Ion Implantation 114 (1989) 286
Silicon, Hydrogenation 114 (1989) 295
Silicon, Optical Properties, Photoresponse, Silicon Alloys 114 (1989) 606
Silicon Alloys, Magnetic Properties 114 (1989) 319
Stäbler–Wronski Effect, Silicon 114 (1989) 636

Photomodulation
Amorphous Solids, Density 114 (1989) 378
Silicon, Doping 114 (1989) 292

Photoresponse
Computer Simulation, Amorphous Solids 114 (1989) 339
Photoinduced Effects, Ion Implantation 114 (1989) 286
Photoinduced Effects, Silicon, Optical Properties, Silicon Alloys 114 (1989) 606

Polymers
Mobility, Transport Properties – Solids 114 (1989) 342

Pressure Effects
Chalcogenides 114 (1989) 31
Chalcogenides, Optical Properties 114 (1989) 130
Chalcogenides, Raman Spectra, Mössbauer Effect 114 (1989) 64

Raman Spectra
Chalcogenides, Hall Coefficient, Structure, EXAFS 114 (1989) 34
Chalcogenides, Mössbauer Effect, Pressure Effects 114 (1989) 64
Deposition Techniques, Silicon Alloys 114 (1989) 528

Dielectric Properties 114 (1989) 813
Germanium, Microstructure, Surface Properties 114 (1989) 675
Hall Coefficient 114 (1989) 37
III–V semiconductors, Ion Implantation, Sputtering, Amorphous Solids 114 (1989) 795
Semiconductors, Structure 114 (1989) 61
Silicon, Optical Properties 114 (1989) 205
Silicon Alloys 114 (1989) 543
Superlattices 114 (1989) 780

Recombination
Amorphous Solids, Carbon, Electron Spin Resonance 114 (1989) 310
Chalcogenides, Ion Implantation 114 (1989) 94
Dangling Bonds, Silicon 114 (1989) 441
Defects, Electronic Structure, Silicon Alloys 114 (1989) 387
Luminescence, Alloys 114 (1989) 283
Photoconductivity, Amorphous Solids, Hopping 114 (1989) 325
Silicon 114 (1989) 313
Silicon, Luminescence 114 (1989) 277
Silicon, Luminescence, Alloys, Silicon Alloys 114 (1989) 280
Silicon, Photoconductivity 114 (1989) 307
Silicon Alloys, Electron Spin Resonance 114 (1989) 549
Silicon Nitride, Relaxation, Luminescence 114 (1989) 570

Reflectivity
Silicon, Stability 114 (1989) 573

Relaxation
Silicon Nitride, Luminescence, Recombination 114 (1989) 570

Rutherford Backscattering
Chalcogenides, Photoinduced Effects 114 (1989) 40

Secondary Electron Emission
Density of States 114 (1989) 432

Secondary Ion Mass Spectroscopy
Silicon Alloys, XPS, Hydrogenation 114 (1989) 474

Semiconductors
Molecular Dynamics, Structure 114 (1989) 7
MultiLayers 114 (1989) 771
Raman Spectra, Structure 114 (1989) 61
Structure 114 (1989) 25

Silica
Capacitance Methods, Silicon 114 (1989) 699

Silicates
Infra-red Absorption 114 (1989) 459

Silicon
Absorption, Density of States 114 (1989) 298
Alloys, Nuclear Magnetic Resonance 114 (1989) 426
Alloys, Structure 114 (1989) 13
Capacitance Methods, Silica 114 (1989) 699
Chalcogenides, Defects 114 (1989) 118
Dangling Bonds, Transistors, Thin Film Transistors 114 (1989) 642
Defects 114 (1989) 178
Defects 114 (1989) 597
Defects 114 (1989) 600
Defects 114 (1989) 627
Defects 114 (1989) 633
Defects, Kinetics 114 (1989) 591
Defects, Optical Properties 114 (1989) 609
Defects, Optical Properties 114 (1989) 738
Defects, Photoconductivity 114 (1989) 660
Defects, Transport Properties – Solids 114 (1989) 639
Defects, Trapping 114 (1989) 615
Density of States, Defects, Hydrogenation, Capacitance Methods, Ion Implantation 114 (1989) 381
Deposition Techniques 114 (1989) 145
Deposition Techniques 114 (1989) 187
Deposition Techniques 114 (1989) 193
Deposition Techniques 114 (1989) 196
Devices 114 (1989) 417
Doping 114 (1989) 654
Doping, Field Effect 114 (1989) 663
Doping, Growth Kinetics 114 (1989) 169
Doping, Ion Implantation 114 (1989) 271
Doping, Metastability 114 (1989) 669
Doping, MultiLayers 114 (1989) 666
Doping, Photoinduced Effects 114 (1989) 289
Electrical Properties, MultiLayers 114 (1989) 301
Electron Spin Resonance 114 (1989) 411
Electron Spin Resonance 114 (1989) 414
Electron Spin Resonance 114 (1989) 729
Electron Spin Resonance, Capacitance Methods, Hydrogenation, Defects 114 (1989) 435
Electron Spin Resonance, Defects, Photoconductivity 114 (1989) 630
Electronic Structure 114 (1989) 238
Electronic Structure 114 (1989) 247
Electronic Structure, Dangling Bonds 114 (1989) 244
Electronic Structure, Defects 114 (1989) 405
Electronic Structure, Density of States 114 (1989) 651
Electronic Structure, Electroabsorption 114 (1989) 250
Ellipsometry 114 (1989) 139
Ellipsometry 114 (1989) 160
EXAFS 114 (1989) 229
Germania, Phonons 114 (1989) 199
Growth Kinetics 114 (1989) 172
Growth Kinetics 114 (1989) 184
Growth Kinetics 114 (1989) 645
Growth Kinetics, Fluorides 114 (1989) 816
Growth Kinetics, Optical Properties, Glow Discharge 114 (1989) 190
Hopping, Computer Simulation, Density of States 114 (1989) 333
Hydrogen Effects, Diffusion 114 (1989) 220

Hydrogen Effects, Growth Kinetics 114 (1989) 810
Hydrogen Effects, Structure 114 (1989) 208
Hydrogenation, Photoinduced Effects 114 (1989) 295
Infra-red Absorption 114 (1989) 163
Infra-red Absorption, Deposition Techniques 114 (1989) 154
Interfaces 114 (1989) 684
Kinetics, Growth Kinetics 114 (1989) 166
Liquid Semiconductors, Germanium 114 (1989) 16
Luminescence, Ion Implantation 114 (1989) 97
Luminescence, Recombination, Alloys, Silicon Alloys 114 (1989) 280
Microstructure, Hydrogenation 114 (1989) 226
Mobility 114 (1989) 447
Mobility, Amorphous Solids, Density of States 114 (1989) 354
Mobility, Defects 114 (1989) 420
Mobility, Transport Properties – Solids 114 (1989) 363
Modelling 114 (1989) 429
Modelling, Theory 114 (1989) 202
MultiLayers, Optical Properties, Silicon Nitride 114 (1989) 723
MultiLayers, Silicon Nitride 114 (1989) 741
Nuclear Magnetic Resonance 114 (1989) 232
Nuclear Magnetic Resonance 114 (1989) 825
Nuclear Magnetic Resonance, Germanium 114 (1989) 235
Optical Properties 114 (1989) 579
Optical Properties, Amorphous Solids 114 (1989) 687
Optical Properties, Nuclear Magnetic Resonance 114 (1989) 408
Oxides, Surface Properties 114 (1989) 678
Photoconductivity 114 (1989) 714
Photoconductivity 114 (1989) 717
Photoconductivity, Density of States 114 (1989) 450
Photoconductivity, Photoinduced Effects 114 (1989) 316
Photoinduced Effects, Optical Properties, Photoresponse, Silicon Alloys 114 (1989) 606
Photoinduced Effects, Stäbler–Wronski Effect 114 (1989) 636
Photomodulation, Doping 114 (1989) 292
Raman Spectra, Optical Properties 114 (1989) 205
Recombination 114 (1989) 313
Recombination, Dangling Bonds 114 (1989) 441
Recombination, Luminescence 114 (1989) 277
Recombination, Photoconductivity 114 (1989) 307
Silicon Alloys, Heat Capacity, Hydrogenation, Crystallization 114 (1989) 211
Silicon Alloys, Photoconductivity 114 (1989) 175
Silicon Alloys, Transport Properties – Devices 114 (1989) 399
Silicon Nitride, MultiLayers, Transport Properties – Solids, Electronic Conductivity 114 (1989) 759
Solar Cells 114 (1989) 181
Stability, Reflectivity 114 (1989) 573
Stäbler–Wronski Effect 114 (1989) 624
Structure, Thin Films 114 (1989) 151
Theory 114 (1989) 402
Theory, Gap States, Electronic Structure 114 (1989) 262
Theory, Growth Kinetics 114 (1989) 157
Theory, Structure 114 (1989) 681
Time-Resolved Spectroscopy 114 (1989) 567
Time-Resolved Spectroscopy, Alloys 114 (1989) 582
Transport Properties – Solids, Photoconductivity, Amorphous Solids 114 (1989) 345
X-ray Absorption, Defects 114 (1989) 223
X-ray Diffraction, Crystallization 114 (1989) 819

Silicon Alloys

Alloys 114 (1989) 672
Alloys, Deposition Techniques 114 (1989) 807
Alloys, Stress Measurement 114 (1989) 510
Defects, Absorption 114 (1989) 702
Defects, Alloys 114 (1989) 462
Defects, Kinetics 114 (1989) 621
Defects, Recombination, Electronic Structure 114 (1989) 387
Density of States, Bonding, X-ray Emission 114 (1989) 483
Deposition Techniques, Raman Spectra 114 (1989) 528
Doping, Defects 114 (1989) 268
Electron Spin Resonance 114 (1989) 423
Electron Spin Resonance 114 (1989) 585
Electronic Structure, Silicon Nitride, XPS 114 (1989) 498
Fermi Level, Surface Reactions 114 (1989) 744
Fluorides 114 (1989) 453
Heterojunctions, Structure 114 (1989) 756
Hydrogen Effects 114 (1989) 804
Infra-red Absorption 114 (1989) 501
Interfaces, Hydrogenation 114 (1989) 753
Luminescence 114 (1989) 507
Luminescence, Nuclear Magnetic Resonance 114 (1989) 522
Magnetic Properties, Photoinduced Effects 114 (1989) 319
Mobility, Optical Properties 114 (1989) 564
MultiLayers, Transport Properties – Solids, Electronic Conductivity 114 (1989) 762
Nuclear Magnetic Resonance, Silicon Nitride 114 (1989) 516
Optical Properties 114 (1989) 322
Optical Properties 114 (1989) 705
Optical Properties, Electrical Properties and Relaxation 114 (1989) 789
Photo-emission 114 (1989) 735
Photoinduced Effects, Silicon, Optical Properties, Photoresponse 114 (1989) 606
Raman Spectra 114 (1989) 543
Recombination, Electron Spin Resonance 114 (1989) 549
Secondary Ion Mass Spectroscopy, XPS, Hydrogenation 114 (1989) 474
Silicon, Heat Capacity, Hydrogenation, Crystallization 114 (1989) 211
Silicon, Luminescence, Recombination, Alloys 114 (1989) 280
Silicon, Photoconductivity 114 (1989) 175
Silicon, Transport Properties – Devices 114 (1989) 399
Solar Cells 114 (1989) 552
Superlattices, Transport Properties – Solids 114 (1989) 693
Surface Properties, Defects 114 (1989) 750
Theory 114 (1989) 513

Thin Films 114 (1989) 801
Transport Properties – Solids 114 (1989) 531
Transport Properties – Solids 114 (1989) 534
Transport Properties – Solids 114 (1989) 537
Transport Properties – Solids 114 (1989) 540
Transport Properties – Solids, Hydrogen Effects 114 (1989) 822
Transport Properties – Solids, Photoconductivity, Defects 114 (1989) 480
X-ray Emission, Silicon Nitride 114 (1989) 492

Silicon Nitride
Electronic Structure, Silicon Alloys, XPS 114 (1989) 498
Microstructure, Dielectric Properties, Infrared Absorption 114 (1989) 489
MultiLayers, Interfaces, Localization 114 (1989) 747
MultiLayers, Optical Properties, Silicon 114 (1989) 723
MultiLayers, Silicon 114 (1989) 741
Relaxation, Luminescence, Recombination 114 (1989) 570
Silicon, MultiLayers, Transport Properties – Solids, Electronic Conductivity 114 (1989) 759
Silicon Alloys, Nuclear Magnetic Resonance 114 (1989) 516
Silicon Alloys, X-ray Emission 114 (1989) 492
X-ray Emission, Theory 114 (1989) 495

Solar Cells
Silicon 114 (1989) 181
Silicon Alloys 114 (1989) 552

Sputtering
III–V semiconductors, Raman Spectra, Ion Implantation, Amorphous Solids 114 (1989) 795

Stability
Silicon, Reflectivity 114 (1989) 573

Stäbler–Wronski Effect
Capacitance Methods 114 (1989) 603
Photoinduced Effects, Silicon 114 (1989) 636
Silicon 114 (1989) 624

Stress Measurement
Alloys, Silicon Alloys 114 (1989) 510

Structure
Chalcogenides 114 (1989) 115
Chalcogenides, Hall Coefficient, EXAFS, Raman Spectra 114 (1989) 34
Germanium, Hydrogenation 114 (1989) 525
Heterojunctions, Silicon Alloys 114 (1989) 756
Mechanical Properties, Elastic Properties 114 (1989) 19
Molecular Dynamics, Semiconductors 114 (1989) 7
Semiconductors 114 (1989) 25
Semiconductors, Raman Spectra 114 (1989) 61
Silicon, Alloys 114 (1989) 13
Silicon, Hydrogen Effects 114 (1989) 208
Silicon, Theory 114 (1989) 681
Silicon, Thin Films 114 (1989) 151

Superlattices
Interfaces 114 (1989) 777
Phonons 114 (1989) 765
Photoconductivity 114 (1989) 720
Raman Spectra 114 (1989) 780
Silicon Alloys, Transport Properties – Solids 114 (1989) 693

Surface Properties
Raman Spectra, Germanium, Microstructure 114 (1989) 675
Silicon, Oxides 114 (1989) 678
Silicon Alloys, Defects 114 (1989) 750

Surface Reactions
Diffusion 114 (1989) 217
Silicon Alloys, Fermi Level 114 (1989) 744

Theory
Chalcogenides, Photoinduced Effects, Optical Properties 114 (1989) 304
Electronic Structure 114 (1989) 253
Electronic Structure 114 (1989) 256
Germania 114 (1989) 708
Liquid Semiconductors, Bonding 114 (1989) 828
Localization, Mobility Edge 114 (1989) 330
Silicon 114 (1989) 402
Silicon, Gap States, Electronic Structure 114 (1989) 262
Silicon, Growth Kinetics 114 (1989) 157
Silicon, Modelling 114 (1989) 202
Silicon, Structure 114 (1989) 681
Silicon Alloys 114 (1989) 513
Silicon Nitride, X-ray Emission 114 (1989) 495
Transport Properties – Solids 114 (1989) 366

Thermoelectric Power
Amorphous Solids 114 (1989) 375

Thin Film Transistors
Silicon, Dangling Bonds, Transistors 114 (1989) 642

Thin Films
Chalcogenides, Optical Properties 114 (1989) 109
Chalcogenides, Photoinduced Effects 114 (1989) 133
Hydrogenation, Optical Properties 114 (1989) 504
Silicon, Structure 114 (1989) 151
Silicon Alloys 114 (1989) 801

Time-Resolved Spectroscopy
Alloys 114 (1989) 588
MultiLayers 114 (1989) 576
Silicon 114 (1989) 567
Silicon, Alloys 114 (1989) 582

Transient Effects
Chalcogenides 114 (1989) 112
Chemical Modification, Chalcogenides 114 (1989) 100
Electronic Structure 114 (1989) 259

Transistors
Silicon, Dangling Bonds, Thin Film Transistors 114 (1989) 642

Transport Properties – Devices
MultiLayers 114 (1989) 711
Silicon, Silicon Alloys 114 (1989) 399

Transport Properties – Solids
Amorphous Solids 114 (1989) 348
Amorphous Solids 114 (1989) 357
Amorphous Solids 114 (1989) 360
Amorphous Solids, Hall Coefficient 114 (1989) 372
Carbon, Hopping 114 (1989) 786
Chalcogenides, Mobility, Differential Thermal Analysis, Glass Transition 114 (1989) 49
Chalcogenides, Photoconductivity 114 (1989) 106
Defects, Silicon 114 (1989) 639
Deposition Techniques, Germania, Glow Discharge, Defects 114 (1989) 477
Hall Coefficient, Amorphous Solids 114 (1989) 369
Microstructure, Optical Properties, Electric Properties 114 (1989) 486
Mobility, Polymers 114 (1989) 342
Mobility, Silicon 114 (1989) 363
Photo Voltage, Mixed-alkali Effect 114 (1989) 1
Photoconductivity 114 (1989) 274
Photoconductivity, Amorphous Solids, Silicon 114 (1989) 345
Silicon, Silicon Nitride, MultiLayers, Electronic Conductivity 114 (1989) 759
Silicon Alloys 114 (1989) 531
Silicon Alloys 114 (1989) 534
Silicon Alloys 114 (1989) 537
Silicon Alloys 114 (1989) 540
Silicon Alloys, Hydrogen Effects 114 (1989) 822
Silicon Alloys, MultiLayers, Electronic Conductivity 114 (1989) 762
Silicon Alloys, Photoconductivity, Defects 114 (1989) 480
Silicon Alloys, Superlattices 114 (1989) 693
Theory 114 (1989) 366

Trapping
Silicon, Defects 114 (1989) 615

X-ray Absorption
Aerogels, Alloys, Optical Properties 114 (1989) 471
Silicon, Defects 114 (1989) 223

X-ray Diffraction
Silicon, Crystallization 114 (1989) 819

X-ray Emission
Silicon Alloys, Density of States, Bonding 114 (1989) 483
Silicon Alloys, Silicon Nitride 114 (1989) 492
Silicon Nitride, Theory 114 (1989) 495

XPS
Electronic Structure, Silicon Alloys, Silicon Nitride 114 (1989) 498
Silicon Alloys, Secondary Ion Mass Spectroscopy, Hydrogenation 114 (1989) 474